

**ISL71001M**

**6A Synchronous Buck Regulator with Integrated MOSFETs**

FN8926  
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The [ISL71001M](#) is a radiation tolerant and high efficiency monolithic synchronous buck regulator with integrated MOSFETs. This single chip power solution operates across an input voltage range of 3V to 5.5V and provides a tightly regulated output voltage that is externally adjustable from 0.8V to ~85% of the input voltage with an output load current capacity of 6A. The ISL71001M is available in a plastic 64 Ld Thin Quad Flatpack (EP-TQFP) package.

The ISL71001M uses peak current-mode control for excellent output load transient response and features integrated compensation and switches at a fixed frequency of 1MHz to reduce component size and count. In applications where two regulators are needed, two ISL71001M devices can be synchronized 180° out-of-phase to reduce the overall input RMS ripple current. The internal synchronous power switches are optimized for high efficiency and good thermal performance.

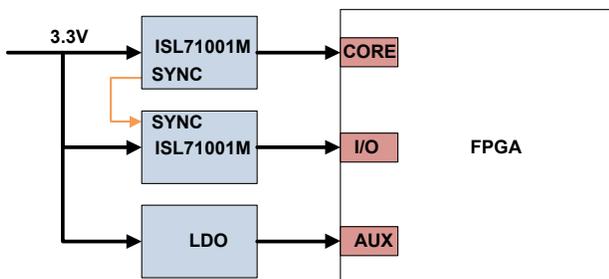
The ISL71001M incorporates fault protection for the regulator. The protection circuits include input undervoltage, output undervoltage, and output overcurrent.

High integration makes the ISL71001M an ideal choice to power many of today’s small form factor applications. Two devices can be synchronized to provide a complete power solution for large scale digital ICs, like Field Programmable Gate Arrays (FPGAs), that require separate core and I/O voltages.

**Related Literature**

For a full list of related documents, visit our website

- [ISL71001M](#) product page



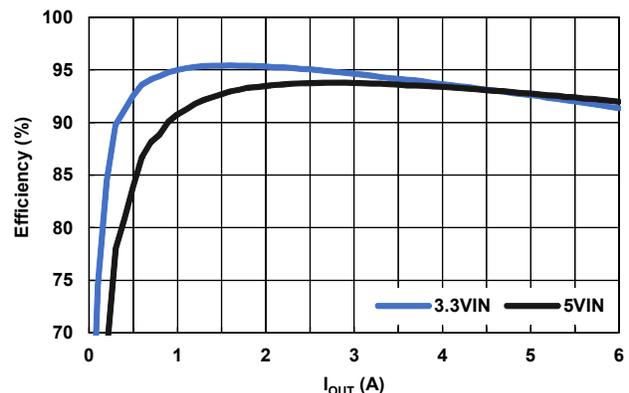
**Figure 1. Typical Application**

**Features**

- Passes NASA low outgassing specifications
- Operates from 3V to 5.5V supply
  - Programmable power-on reset level
- Current mode control for excellent dynamic response
- Fixed 1MHz switching frequency
- ±1.2% reference voltage
- Thermally enhanced heat-sink plastic package
- Highly efficient: 95% peak efficiency
- Bidirectional SYNC pin allows two devices to be synchronized 180° out-of-phase
- Adjustable output voltage
- Analog soft-start
- Output undervoltage and output overcurrent protection
- Power-good output voltage monitor
- Tin (Sn) free lead finish
- Characterized radiation level
  - 30krad(Si) at a low dose rate
  - Single-event effects at LET = 43MeV•cm<sup>2</sup>/mg

**Applications**

- FPGA, CPLD, DSP, CPU Core, or I/O voltages
- Low-voltage, high-density distributed power systems
- Low Earth Orbit (LEO) applications
- High altitude avionics
- Launch vehicles



**Figure 2. Efficiency vs V<sub>IN</sub> for 2.5V Output, T<sub>C</sub> = +25°C**

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# 1. Overview

## 1.1 Typical Application Schematics

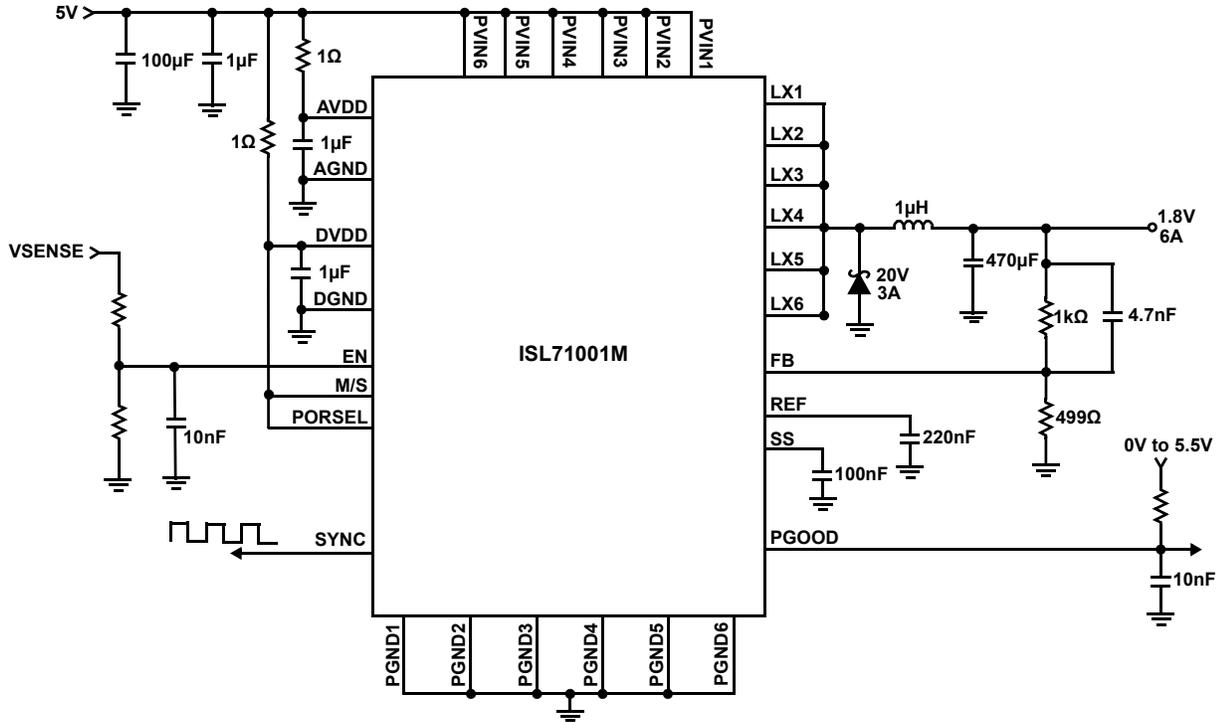


Figure 3. 5V Input Supply Voltage with Master Mode Synchronization

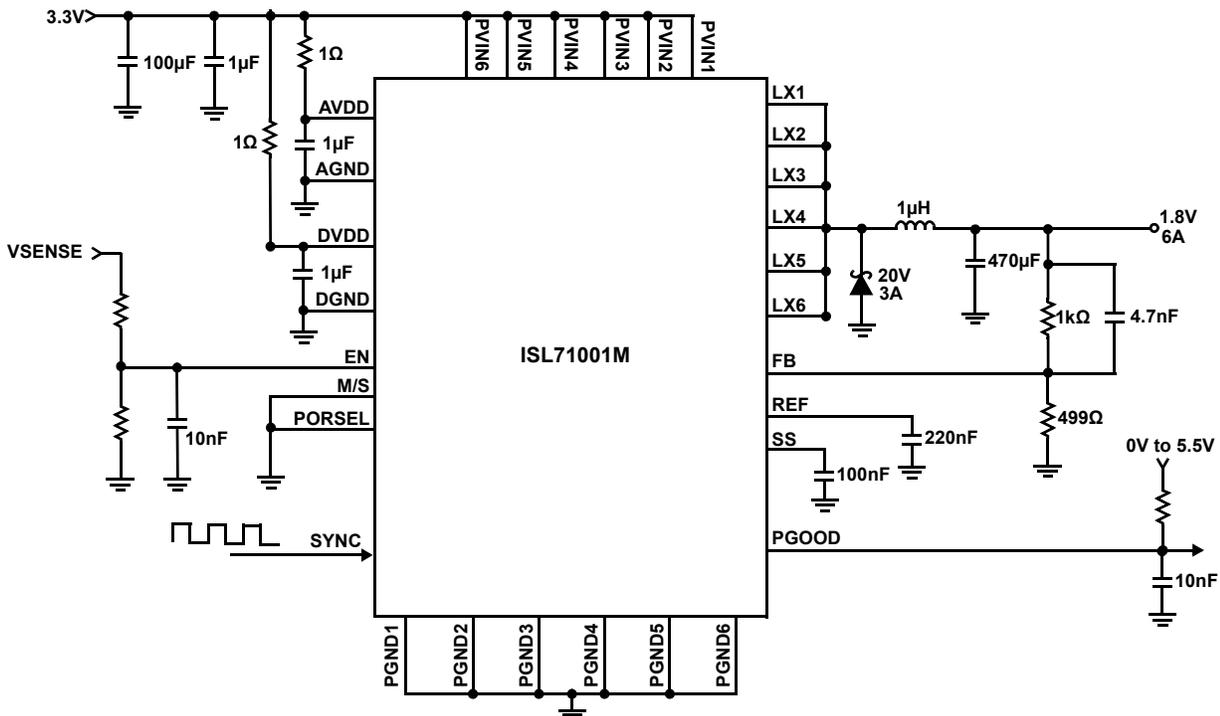


Figure 4. 3.3V Input Supply Voltage with Clock Slave Mode Synchronization

## 1.2 Functional Block Diagram

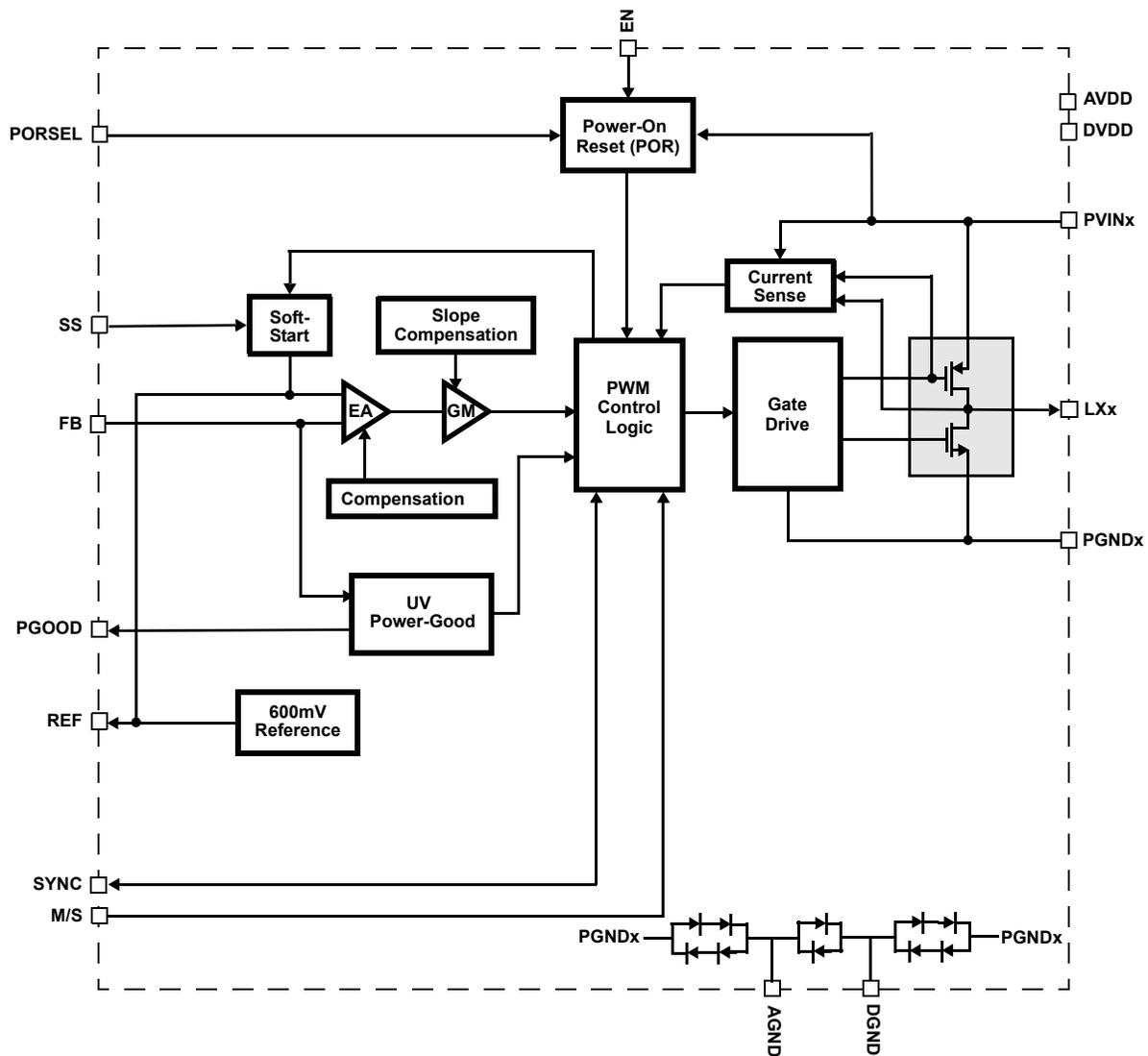


Figure 5. Block Diagram

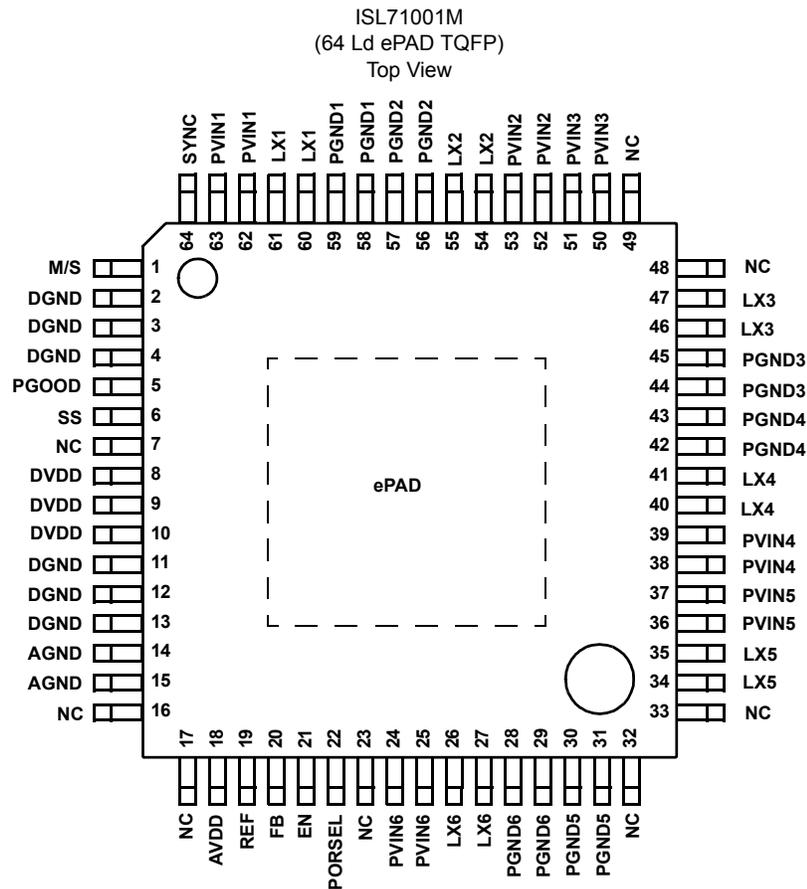
## 1.3 Ordering Information

Part Number (Notes 1, 2, 3)	Part Marking	Temp. Range (°C)	Tape and Reel (Units)	Package (RoHS Compliant)	Pkg. Dwg. #
ISL71001MNZ	71001MNZ	-55 to +125	-	64 Ld ePAD TQFP	Q64.10x10J
ISL71001MNZ-T	71001MNZ	-55 to +125	1k	64 Ld ePAD TQFP	Q64.10x10J
ISL71001MEVAL1Z	Evaluation Board				

Notes:

1. Refer to [TB347](#) for details about reel specifications.
2. These Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu-Ag plate -e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
3. For Moisture Sensitivity Level (MSL), see the [ISL71001M](#) product information page. For more information about MSL, see [TB363](#).

## 1.4 Pin Configuration



## 1.5 Pin Descriptions

Pin Number	Pin Name	Description
1	M/S	Master/Slave input for selecting the direction of the bidirectional SYNC pin. For SYNC = Output (Master mode), connect this pin to DVDD. For SYNC = Input (Slave Mode), connect this pin to DGND.
2, 3, 4, 11, 12, 13	DGND	The digital ground associated with the internal digital control circuitry. Connect these pins directly to the ground plane.
5	PGOOD	Power-good output. This pin is an open-drain logic output that is pulled to DGND when the output voltage is outside a $\pm 11\%$ typical regulation window. This pin can be pulled up to any voltage from 0V to 5.5V, independent of the supply voltage. A nominal 1k $\Omega$ to 10k $\Omega$ pull-up resistor is recommended. Bypass this pin to DGND with a 10nF ceramic capacitor to mitigate SEE.
6	SS	The soft-start input. Connect a ceramic capacitor from this pin to AGND to set the soft-start output ramp time in accordance with <a href="#">Equation 1</a> : $(EQ. 1) \quad t_{SS} = C_{SS} \cdot V_{REF} / I_{SS}$ where: $t_{SS}$ = Soft-start output ramp time $C_{SS}$ = Soft-start capacitor $V_{REF}$ = Reference voltage (0.6V typical) $I_{SS}$ = Soft-start charging current (23 $\mu$ A typical) Soft-start time is adjustable from approximately 2ms to 200ms. The range of the soft-start capacitor should be 82nF to 8.2 $\mu$ F, inclusive.

Pin Number	Pin Name	Description
7, 16, 17, 23, 32, 33, 48, 49	NC	There is no internal connection on this pin
8, 9, 10	DVDD	Bias supply inputs to the internal digital control circuitry. Connect these pins together at the IC and locally filter them to DGND using a 1Ω resistor and a 1μF ceramic capacitor. Locate both filter components as close as possible to the IC.
14, 15	AGND	Analog ground associated with the internal analog control circuitry. Connect these pins directly to the ground plane.
18	AVDD	Bias supply input to the internal analog control circuitry. Locally filter this pin to AGND using a 1Ω resistor and a 1μF ceramic capacitor. Locate both filter components as close as possible to the IC.
19	REF	Internal reference voltage output. Bypass this pin to AGND with a 220nF ceramic capacitor located as close as possible to the IC. The bypass capacitor is needed to mitigate SEE. No current (sourcing or sinking) is available from this pin.
20	FB	Voltage feedback input to the internal error amplifier. Connect a resistor from FB to VOUT and from FB to AGND to adjust the output voltage in accordance with <a href="#">Equation 2</a> : $(EQ. 2) \quad V_{OUT} = V_{REF} \cdot [1 + (R_T/R_B)]$ where: $V_{OUT}$ = Output voltage $V_{REF}$ = Reference voltage (0.6V typical) $R_T$ = Top divider resistor (Must be 1kΩ) $R_B$ = Bottom divider resistor The top divider resistor must be 1kΩ to mitigate SEE. Connect a 4.7nF ceramic capacitor across $R_T$ to mitigate SEE and to improve stability margins.
21	EN	Enable input to the IC. This is a comparator type input with a rising threshold of 0.6V and programmable hysteresis. Driving this pin above 0.6V enables the IC. Bypass this pin to AGND with a 10nF ceramic capacitor to mitigate SEE.
22	PORSEL	Input for selecting the rising and falling POR (Power-On-Reset) thresholds. For a nominal 5V supply, connect this pin to DVDD. For a nominal 3.3V supply, connect this pin to DGND. For nominal supply voltages between 5V and 3.3V, connect this pin to DGND.
24, 25, 36, 37, 38, 39, 50, 51, 52, 53, 62, 63	PVINx	Power supply inputs to the corresponding internal power blocks. These pins must be connected to a common power supply rail, which must fall in the range of 3V to 5.5V. Bypass these pins directly to PGNDx with ceramic capacitors located as close as possible to the IC.
26, 27, 34, 35, 40, 41, 46, 47, 54, 55, 60, 61	LXx	Outputs of the corresponding internal power blocks and should be connected to the output filter inductor. Internally, these pins are connected to the synchronous MOSFET power switches. To minimize voltage undershoot, it is recommended that a Schottky diode be connected from these pins to PGNDx. The Schottky diode should be located as close as possible to the IC.
28, 29, 30, 31, 42, 43, 44, 45, 56, 57, 58, 59	PGNDx	Power grounds associated with the corresponding internal power blocks. Connect these pins directly to the ground plane. These pins should also connect to the negative terminals of the input and output capacitors. Locate the input and output capacitors as close as possible to the IC.
64	SYNC	Synchronization I/O for the IC. When configured as an output (Master mode), this pin drives the SYNC input of another ISL71001M. When configured as an input (Slave mode), this pin accepts the SYNC output from another ISL71001M or an external clock. Synchronization of the slave unit is 180° out-of-phase with respect to the master unit. If synchronizing to an external clock, the clock must be SEE hardened and the frequency must be within the range of 1MHz ±20%.
EPAD	Heatsink	Bottom thermal pad. It is not connected to any electrical potential of the IC. In the layout, it must be connected to a PCB large ground copper plane that doesn't contain noisy power flows. Put multiple vias (as many as possible) in this pad connecting to the ground copper plane, to help reduce the IC's $\theta_{JA}$ .

## 2. Specifications

### 2.1 Absolute Maximum Ratings

Parameter	Minimum	Maximum	Unit
AVDD, DVDD, LXx, PVINx	GND - 0.3	6.5	V
Signal Pins (EN, FB, PORSEL, and REF)		AVDD	
Digital Control Pins (M/S, SYNC)		DVDD	
PGOOD	GND - 0.3	6.5	V
SS	GND - 0.3	2.5	V
DC Current per Phase		1.2	A
ESD Rating	Rating		Unit
Human Body Model (Tested per JS-001-2014)	4		kV
Charged Device Model (Tested per JS-002-2014)	2		kV
Machine Model (Tested per JESD22-A115C)	200		V
Latch-Up (Tested per JESD-78E; Class 2, Level A)	100		mA

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

### 2.2 Outgas Testing

Specification (Tested per ASTM E595, 1.5)	Value	Unit
Total Mass Loss ( <a href="#">Note 4</a> )	0.06	%
Collected Volatile Condensable Material ( <a href="#">Note 4</a> )	<0.01	%
Water Vapor Recovered	0.03	%

Note:

4. Outgassing results meet NASA requirements of total mass loss <1% and collected volatile condensable material of <0.1%.

### 2.3 Thermal Information

Thermal Resistance (Typical)	$\theta_{JA}$ (°C/W)	$\theta_{JC}$ (°C/W)
64 Ld EP-TQFP Package ( <a href="#">Notes 5, 6</a> )	21	0.5

Notes:

5.  $\theta_{JA}$  is measured in free air with the component mounted on a high-effective thermal conductivity test board with "direct attach" features. See [TB379](#).
6. For  $\theta_{JC}$ , the "case temp" location is the center of the exposed metal pad on the package underside.

Parameter	Minimum	Maximum	Unit
Max Continuous Package Power Dissipation		400	mW
Storage Temperature Range	-55	+125	°C
Maximum Operating Junction Temperature		+145	°C
Pb-Free Reflow Profile	see <a href="#">TB493</a>		

## 2.4 Recommended Operation Conditions

Parameter	Minimum	Maximum	Unit
AVDD, DVDD, LXx, PVINx	3	5.5	V
Signal Pins (EN, FB, PORSEL, and REF)		AVDD	
Digital Pins (M/S, SYNC)		DVDD	
REF, SS		Internally Set	V
$I_{LXx}$ ( $T_J \leq +145^\circ\text{C}$ )	0	1.0	A
Ambient Temperature Range	-55	+125	$^\circ\text{C}$

## 2.5 Electrical Specifications

Unless otherwise noted,  $V_{IN} = AVDD = DVDD = PVINx = EN = M/S = 3V$  or  $5.5V$ ;  $GND = AGND = DGND = PGNDx = 0V$ ;  $FB = 0.65V$ ;  $PORSEL = V_{IN}$  for  $4.5V \leq V_{IN} \leq 5.5V$  and  $GND$  for  $V_{IN} < 4.5V$ ;  $SYNC = LXx = \text{open circuit}$ ;  $PGOOD$  is pulled up to  $V_{IN}$  with a 1k resistor;  $REF$  is bypassed to  $GND$  with a 220nF capacitor;  $SS$  is bypassed to  $GND$  with a 100nF capacitor;  $I_{OUT} = 0A$ ;  $T_A = T_J = +25^\circ\text{C}$  (Note 9). **Boldface limits apply across the operating temperature range,  $-55^\circ\text{C}$  to  $+125^\circ\text{C}$ .** Production tested at  $+25^\circ\text{C}$  (Note 10).

Parameter	Test Conditions	Min (Note 10)	Typ (Note 9)	Max (Note 10)	Unit
<b>Power Supply</b>					
Operating Supply Current	$V_{IN} = 5.5V$ (Note 7)		40	<b>65</b>	mA
	$V_{IN} = 3.6V$ (Note 7)		25	<b>45</b>	mA
Shutdown Supply Current	$V_{IN} = 5.5V$ , $EN = GND$ (Note 8)		2	<b>6</b>	mA
	$V_{IN} = 3.6V$ , $EN = GND$ (Note 8)		1.4	<b>4.5</b>	mA
<b>Output Voltage</b>					
Reference Voltage Tolerance		<b>0.593</b>	0.6	<b>0.607</b>	V
Feedback (FB) Input Leakage Current	$V_{IN} = 5.5V$ , $V_{FB} = 0.6V$	<b>-1</b>	0	<b>1</b>	$\mu\text{A}$
<b>PWM Control Logic</b>					
Oscillator Accuracy		<b>0.82</b>	1	<b>1.18</b>	MHz
External Oscillator Range		<b>0.8</b>	1	<b>1.2</b>	MHz
Minimum LXx On Time	$V_{IN} = 5.5V$ , Test mode		107	<b>150</b>	ns
Minimum LXx Off Time	$V_{IN} = 5.5V$ , Test mode		41	<b>100</b>	ns
Minimum LXx On Time	$V_{IN} = 3.6V$ , Test mode		142	<b>210</b>	ns
Minimum LXx Off Time	$V_{IN} = 3.6V$ , Test mode		41	<b>100</b>	ns
Master/Slave (M/S) Input Voltage	Input high threshold	<b><math>V_{IN} - 0.5</math></b>	1.9		V
	Input low threshold		1.3	<b>0.5</b>	V
Master/Slave (M/S) Input Leakage Current	$V_{IN} = 5.5V$ , $M/S = GND$ or $V_{IN}$	<b>-1</b>	0	<b>1</b>	$\mu\text{A}$
Synchronization (SYNC) Input Voltage	Input high threshold, $M/S = GND$	<b>2.3</b>	1.7		V
	Input low threshold, $M/S = GND$		1.5	<b>1</b>	V
Synchronization (SYNC) Input Leakage Current	$V_{IN} = 5.5V$ , $M/S = GND$ , $SYNC = GND$ or $V_{IN}$	<b>-1</b>	0	<b>1</b>	$\mu\text{A}$
Synchronization (SYNC) Output Voltage	$V_{IN} - V_{OH}$ at $I_{OH} = -1\text{mA}$		0.16	<b>0.4</b>	V
	$V_{OL}$ at $I_{OL} = 1\text{mA}$		0.14	<b>0.4</b>	V
<b>Power Blocks</b>					
Upper Device $r_{DS(ON)}$	$V_{IN} = 3V$ , 0.4A per power block, Test mode	<b>80</b>	142	<b>220</b>	m $\Omega$
Lower Device $r_{DS(ON)}$	$V_{IN} = 3V$ , 0.4A per power block, Test mode	<b>40</b>	85	<b>140</b>	m $\Omega$

Unless otherwise noted,  $V_{IN} = AVDD = DVDD = PVINx = EN = M/S = 3V$  or  $5.5V$ ;  $GND = AGND = DGND = PGNDx = 0V$ ;  $FB = 0.65V$ ;  $PORSEL = V_{IN}$  for  $4.5V \leq V_{IN} \leq 5.5V$  and  $GND$  for  $V_{IN} < 4.5V$ ;  $SYNC = LXx =$  open circuit;  $PGOOD$  is pulled up to  $V_{IN}$  with a  $1k$  resistor;  $REF$  is bypassed to  $GND$  with a  $220nF$  capacitor;  $SS$  is bypassed to  $GND$  with a  $100nF$  capacitor;  $I_{OUT} = 0A$ ;  $T_A = T_J = +25^\circ C$  (Note 9). **Boldface limits apply across the operating temperature range,  $-55^\circ C$  to  $+125^\circ C$ .** Production tested at  $+25^\circ C$  (Note 10). (Continued)

Parameter	Test Conditions	Min (Note 10)	Typ (Note 9)	Max (Note 10)	Unit
LXx Output Leakage	$V_{IN} = 5.5V$ , $EN = LXx = GND$ , single LXx output	-1	0	1	$\mu A$
	$V_{IN} = 5.5V$ , $EN = GND$ , $LXx = V_{IN}$ , single LXx output	-15	0	15	$\mu A$
Dead Time	Within a single power block or between power blocks (Note 10)	1.7	5		ns
Efficiency	$V_{IN} = 3.3V$ , $V_{OUT} = 1.8V$ , $I_{OUT} = 3A$		94		%
	$V_{IN} = 5V$ , $V_{OUT} = 3.3V$ , $I_{OUT} = 3A$		95		%
<b>Power-On Reset</b>					
POR Select (PORSEL)	Input high threshold	$V_{IN} - 0.5$	1.4		V
	Input low threshold		1.3	0.5	V
POR Select (PORSEL) Input Leakage Current	$V_{IN} = 5.5V$ , $PORSEL = GND$ or $V_{IN}$	-1	0	1	$\mu A$
VIN POR	Rising threshold, $PORSEL = V_{IN}$	4.1	4.28	4.45	V
	Hysteresis, $PORSEL = V_{IN}$	225	331	425	mV
	Rising threshold, $PORSEL = GND$	2.65	2.8	2.95	V
	Hysteresis, $PORSEL = GND$	90	168	260	mV
Enable (EN) Input Voltage	Rising/falling threshold	0.56	0.6	0.64	V
Enable (EN) Input Leakage Current	$V_{IN} = 5.5V$ , $EN = GND$ or $V_{IN}$	-3	0	3	$\mu A$
Enable (EN) Sink Current	$EN = 0.3V$	6.4	11	16.6	$\mu A$
<b>Soft-Start</b>					
Soft-Start Source Current	$SS = GND$	20	23	27	$\mu A$
Soft-Start Discharge ON-Resistance			2.1	4.7	$\Omega$
Soft-Start Discharge Time			256		Clock Cycles
<b>Power-Good Signal</b>					
Rising Threshold	$V_{FB}$ as a percent of $V_{REF}$ , Test mode	107	112	115	%
Rising Hysteresis	$V_{FB}$ as a percent of $V_{REF}$ , Test mode	2	3.7	5	%
Falling Threshold	$V_{FB}$ as a percent of $V_{REF}$ , Test mode	85	88	93	%
Falling Hysteresis	$V_{FB}$ as a percent of $V_{REF}$ , Test mode	2	3.6	5	%
Power-Good Drive	$V_{IN} = 3V$ , $PGOOD = 0.4V$ , $EN = GND$	7.3	8.2		mA
Power-Good Leakage	$V_{IN} = PGOOD = 5.5V$		0.001	1	$\mu A$
<b>Protection Features</b>					
Undervoltage Monitor					
Undervoltage Trip Threshold	$V_{IN} = 3V$ , $V_{FB}$ as a percent of $V_{REF}$ , Test mode	71	75	79	%
Undervoltage Recovery Threshold	$V_{IN} = 3V$ , $V_{FB}$ as a percent of $V_{REF}$ , Test mode	84	88	92	%
<b>Overcurrent Monitor</b>					
Overcurrent Trip Level	LX4 power block, Test mode	1.3	1.7	2.5	A
Overcurrent Trip Counts	LX4 power block, Test mode (Note 10)		2		
Overcurrent or Short-Circuit Duty-Cycle	$V_{IN} = 3V$ , $SS$ interval = $200\mu s$ , Test mode, fault interval divided by hiccup interval		0.8	5	%

Unless otherwise noted,  $V_{IN} = AVDD = DVDD = PVINx = EN = M/S = 3V$  or  $5.5V$ ;  $GND = AGND = DGND = PGNDx = 0V$ ;  $FB = 0.65V$ ;  $PORSEL = V_{IN}$  for  $4.5V \leq V_{IN} \leq 5.5V$  and  $GND$  for  $V_{IN} < 4.5V$ ;  $SYNC = LXx =$  open circuit;  $PGOOD$  is pulled up to  $V_{IN}$  with a  $1k$  resistor;  $REF$  is bypassed to  $GND$  with a  $220nF$  capacitor;  $SS$  is bypassed to  $GND$  with a  $100nF$  capacitor;  $I_{OUT} = 0A$ ;  $T_A = T_J = +25^\circ C$  (Note 9). **Boldface limits apply across the operating temperature range,  $-55^\circ C$  to  $+125^\circ C$ .** Production tested at  $+25^\circ C$  (Note 10). (Continued)

Parameter	Test Conditions	Min (Note 10)	Typ (Note 9)	Max (Note 10)	Unit
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Notes:

7.  $L = 1\mu H$  connected to  $Lx$ .
8.  $1k\Omega$   $PGOOD$  pull-up resistor is not populated.
9. Typical values shown are not guaranteed.
10. Compliance to datasheet limits is assured by one or more methods: analysis, characterization, design, or production test

### 3. Typical Operating Performance

Unless otherwise noted,  $T_A = +25^\circ\text{C}$ ,  $V_{IN} = 5\text{V}$ ,  $EN = 5\text{V}$ ,  $L = 1.0\mu\text{H}$ ,  $C_{IN} = 2 \times 47\mu\text{F}$ ,  $C_{OUT} = 3 \times 47\mu\text{F}$  and  $1 \times 150\mu\text{F}$ ,  $V_{OUT} = 1.2\text{V}$ .

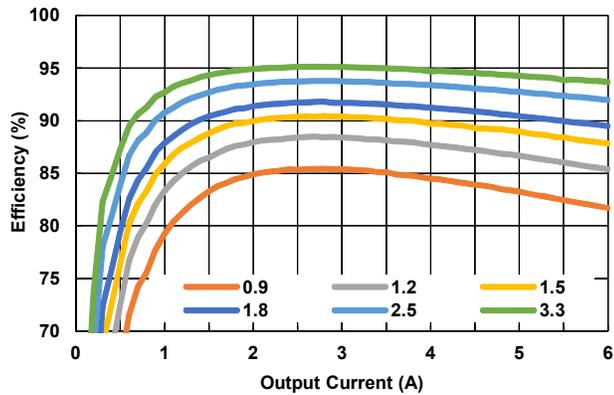


Figure 6. 5V  $V_{IN}$  Efficiency for Multiple  $V_{OUT}$  Levels

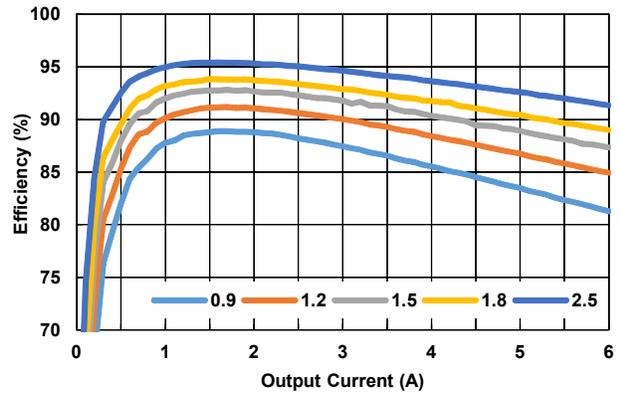


Figure 7. 3.3V  $V_{IN}$  Efficiency for Multiple  $V_{OUT}$  Levels

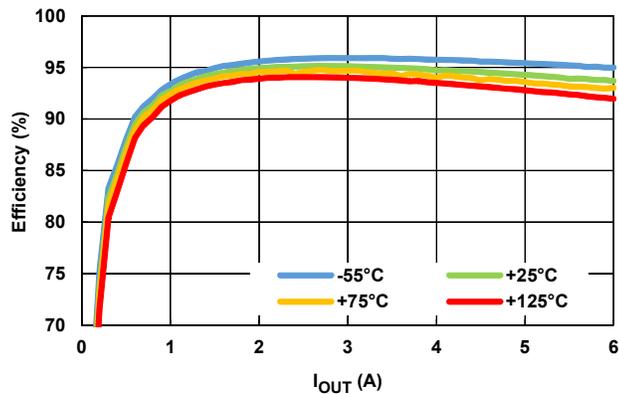


Figure 8. 5V  $V_{IN}$  Efficiency, 3.3V  $V_{OUT}$  Over Temperature

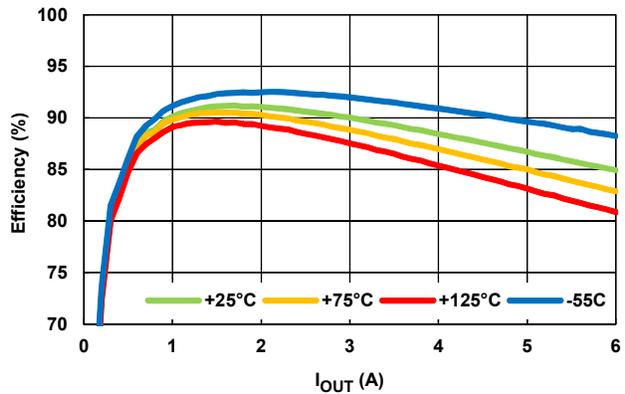


Figure 9. 3.3V  $V_{IN}$  Efficiency, 1.2V  $V_{OUT}$  Over Temperature

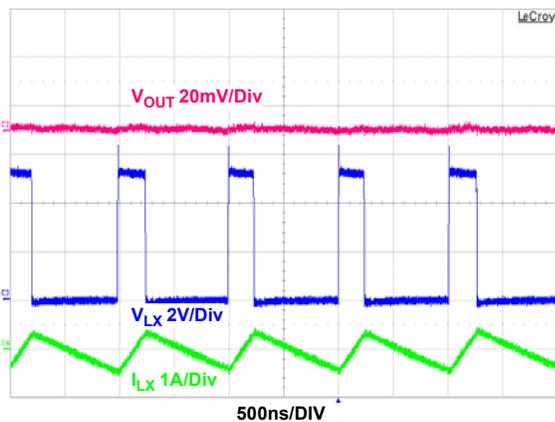


Figure 10. LX,  $V_{OUT}$  and Inductor Current Waveforms,  $I_O = 0\text{A}$

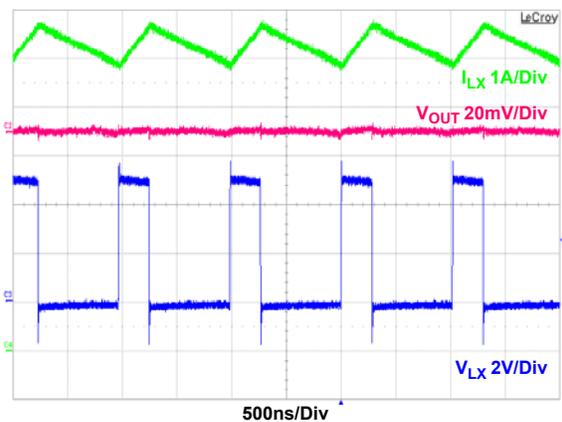


Figure 11. LX,  $V_{OUT}$  and Inductor Current Waveforms,  $I_O = 6\text{A}$

Unless otherwise noted,  $T_A = +25^\circ\text{C}$ ,  $V_{IN} = 5\text{V}$ ,  $EN = 5\text{V}$ ,  $L = 1.0\mu\text{H}$ ,  $C_{IN} = 2 \times 47\mu\text{F}$ ,  $C_{OUT} = 3 \times 47\mu\text{F}$  and  $1 \times 150\mu\text{F}$ ,  $V_{OUT} = 1.2\text{V}$ . (Continued)

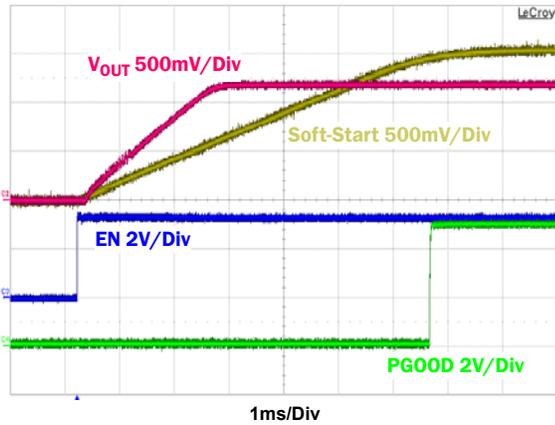


Figure 12. Enabled Start-Up Waveforms

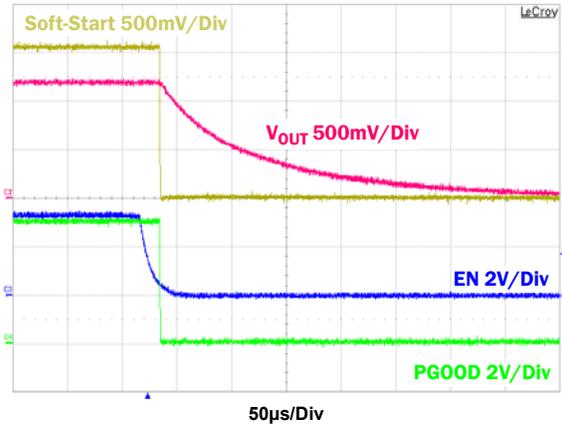


Figure 13. Disabled Turn-Off Waveforms

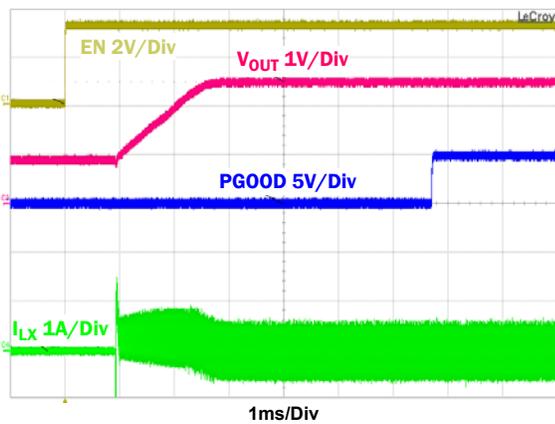


Figure 14. 0.5V Prebiased Start-Up to 2.5V  $V_{OUT}$  Waveforms  $I_O = 0\text{A}$

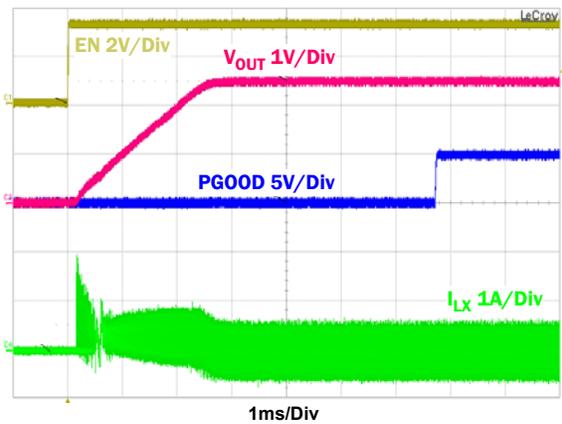


Figure 15. Start-Up to 2.5V  $V_{OUT}$  Waveforms  $I_O = 0\text{A}$

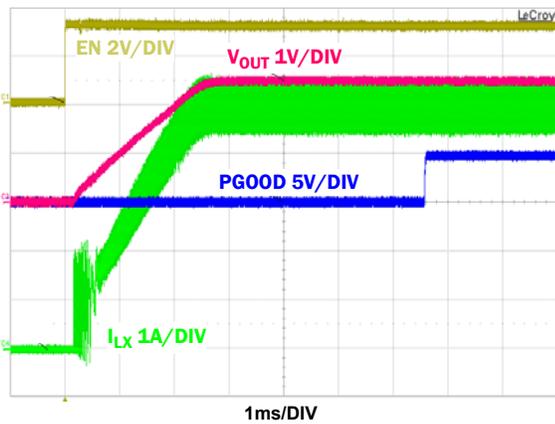


Figure 16. Start-Up to 2.5V  $V_{OUT}$  Waveforms  $I_O = 5\text{A}$

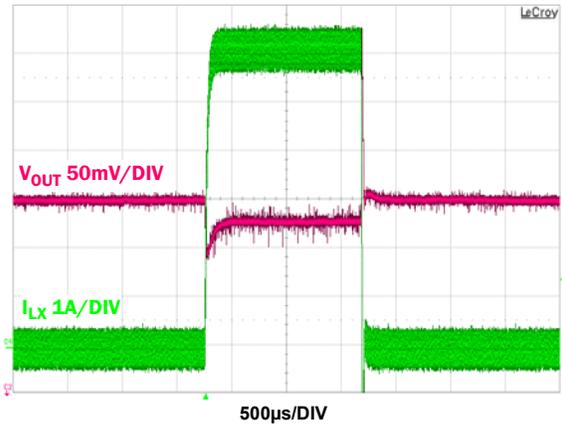


Figure 17. Load Transient 0 to 6A

Unless otherwise noted,  $T_A = +25^\circ\text{C}$ ,  $V_{IN} = 5\text{V}$ ,  $EN = 5\text{V}$ ,  $L = 1.0\mu\text{H}$ ,  $C_{IN} = 2 \times 47\mu\text{F}$ ,  $C_{OUT} = 3 \times 47\mu\text{F}$  and  $1 \times 150\mu\text{F}$ ,  $V_{OUT} = 1.2\text{V}$ . (Continued)

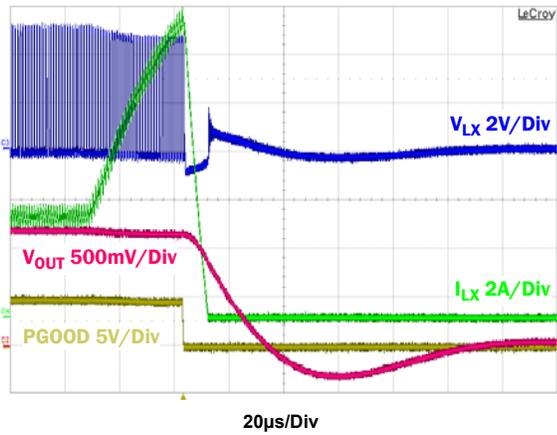


Figure 18. Into Overcurrent Waveforms

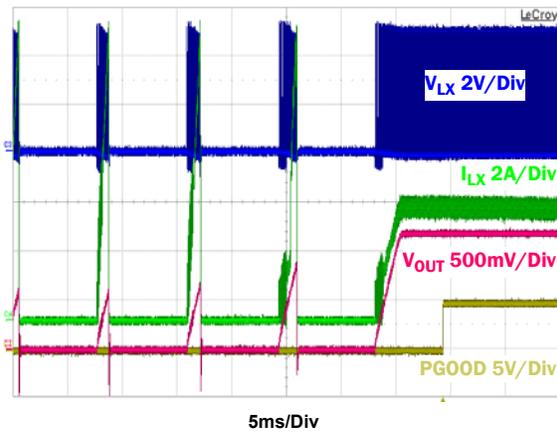


Figure 19. Out of Overcurrent Recovery Waveforms

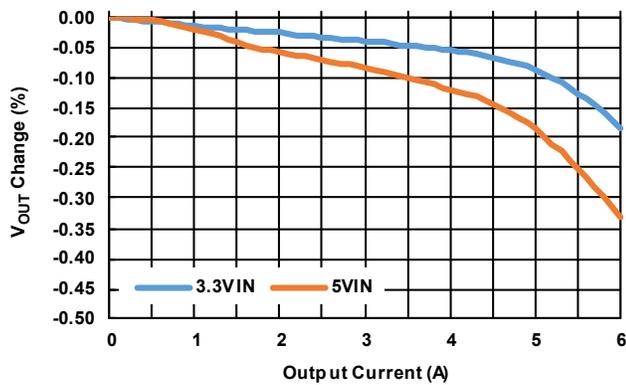


Figure 20.  $V_{IN}$  Load Regulation 1.2V  $V_{OUT}$

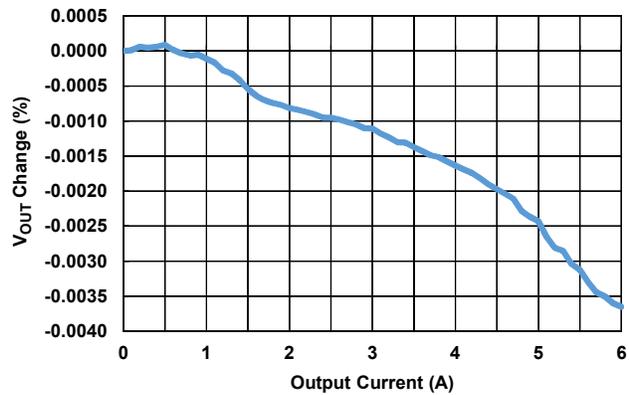


Figure 21.  $V_{IN}$  Line Regulation,  $V_{OUT} = 2.5\text{V}$  ( $5\text{V}_{IN} - 3.3\text{V}_{IN}$ )

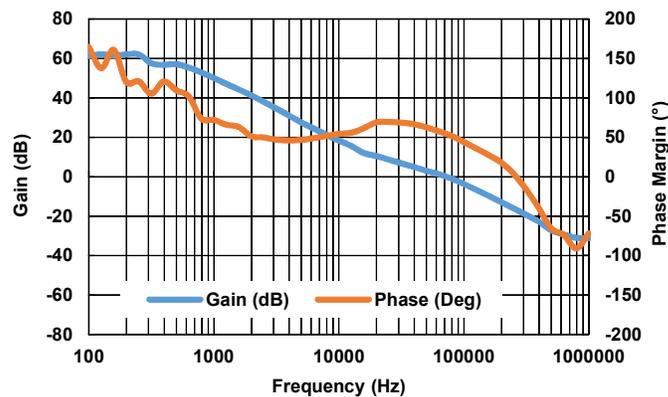


Figure 22. Gain Phase Graph

## 4. Device Information

### 4.1 Functional Description

The ISL71001M is a monolithic, fixed frequency, current-mode synchronous buck regulator with user-configurable power blocks. Two ISL71001M devices can be used to provide a total DC/DC solution for FPGAs, CPLDs, DSPs, and CPUs.

#### 4.1.1 Power Blocks

The power output stage of the regulator consists of six 1A capable power blocks that are paralleled to provide full 6A output current capability. The block diagram in [Figure 23](#) shows a top level view of the individual power blocks.

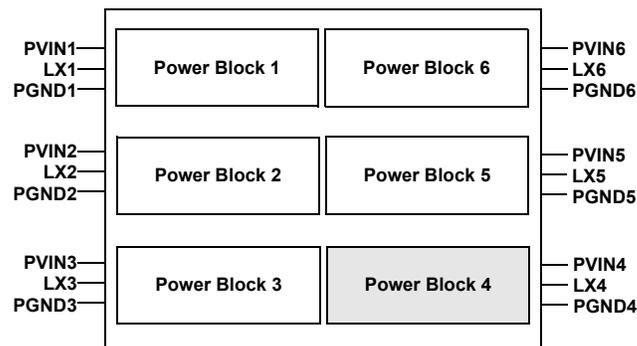


Figure 23. Power Block Diagram

Each power block has a power supply input pin, PVINx, a phase output pin, LXx, and a power supply ground pin, PGNDx. All PVINx pins must be connected to a common power supply rail and all PGNDx pins must be connected to a common ground. The LXx pins should be connected to the output inductor based on the required load current, but must include the LX4 pin. For example, if 3A of output current is needed, any three LXx pins can be connected to the inductor as long as one of them is the LX4 pin. The unused LXx pins should be left unconnected. Connecting all six LXx pins to the output inductor provides a maximum 6A of output current. See the [“Typical Application Schematic” on page 6](#) for pin connection guidance.

A scaled pilot device associated with each power block provides current feedback. Power Block 4 contains the master pilot device and this is why it must be connected to the output inductor.

#### 4.1.2 Main Control Loop

During normal operation, the internal top power switch is turned on at the beginning of each clock cycle. Current in the output inductor ramps up until the current comparator trips and turns off the top power MOSFET. The bottom power MOSFET turns on and the inductor current ramps down for the rest of the cycle.

The current comparator compares the output current at the ripple current peak to a current pilot. The error amplifier monitors  $V_{OUT}$  and compares it with an internal reference voltage. The output voltage of the error amplifier drives a proportional current to the pilot. If  $V_{OUT}$  is low, the current level of the pilot is increased and the trip off current level of the output is increased. The increased output current raises  $V_{OUT}$  until it is in agreement with the reference voltage.

### 4.1.3 Output Voltage Selection

The output voltage of the ISL71001M can be adjusted using an external resistor divider as shown in [Figure 24](#).

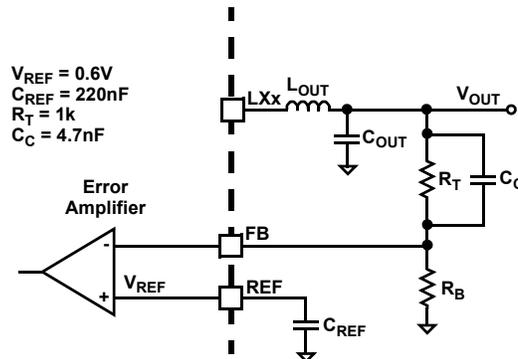


Figure 24. Output Voltage Selection

$R_T$  should be selected as  $1k\Omega$  to mitigate single event transients.  $R_T$  should be shunted by a  $4.7nF$  ceramic capacitor,  $C_C$ , to mitigate single event transients and to improve loop stability margins. The REF pin should be bypassed to AGND with a  $220nF$  ceramic capacitor to mitigate single-event transients. It should be noted that no current (sourcing or sinking) is available from the REF pin.  $R_B$  can be determined from [Equation 3](#). The designer can configure the output voltage from  $0.8V$  to  $85\%$  of the input voltage.

$$(EQ. 3) \quad R_B = R_T \cdot \frac{V_{REF}}{V_{OUT} - V_{REF}}$$

### 4.1.4 Switching Frequency/Synchronization

The ISL71001M features an internal oscillator running at a fixed frequency of  $1MHz$ . The regulator can be configured to run from the internal oscillator or can be synchronized to another ISL71001M or an external clock with a frequency range of  $1MHz \pm 20\%$ .

To run the regulator from the internal oscillator, connect the M/S pin to DVDD. In this case, the output of the internal oscillator appears on the SYNC pin. To synchronize the regulator to an external clock, connect the M/S pin to DGND. In this case, the SYNC pin is an input that accepts an external synchronizing signal. When synchronizing multiple devices, slave regulators are synchronized  $180^\circ$  out-of-phase with respect to the external clock.

## 4.2 Operation Initialization

The ISL71001M initializes based on the state of the Power-On Reset (POR) monitor of the PVINx inputs and the state of the EN input. Successful initialization prompts a soft-start interval, and the regulator begins slowly ramping the output voltage. Once the commanded output voltage is within the proper window of operation, the power-good signal changes state from low to high, indicating proper regulator operation.

### 4.2.1 Power-On Reset

The POR circuitry prevents the controller from attempting to soft-start before sufficient bias is present at the PVINx pins.

The POR threshold of the PVINx pins is controlled by the PORSEL pin. For a nominal  $5V$  supply voltage, PORSEL should be connected to DVDD. For a nominal  $3.3V$  supply voltage, PORSEL should be connected to DGND. For nominal supply voltages between  $5V$  and  $3.3V$ , PORSEL should be connected to DGND. The POR rising and falling thresholds are shown in the “Electrical Specifications” table on [page 10](#).

Hysteresis between the rising and falling thresholds ensures that small perturbations on PVINx seen during turn-on/turn-off of the regulator do not cause inadvertent turn-off/turn-on of the regulator. When the PVINx

pins are below the POR rising threshold, the internal synchronous power MOSFET switches are turned off, and the LX pins are held in a high-impedance state.

#### 4.2.2 Enable and Disable

After the POR input requirement is met, the ISL71001M remains in shutdown until the voltage at the enable input rises above the enable threshold. As shown in [Figure 25](#), the enable circuit features a comparator-type input. In addition to simple logic on/off control, the enable circuit allows the level of an external voltage to precisely gate the turn-on/turn-off of the regulator. An internal  $I_{EN}$  current sink with a typical value of  $11\mu\text{A}$  is only active when the voltage on the EN pin is below the enable threshold. The current sink pulls the EN pin low. As  $V_{IN2}$  rises, the enable level is not set exclusively by the resistor divider from  $V_{IN2}$ .

With the current sink active, the enable level is defined by [Equation 4](#).  $R_1$  is the resistor from the EN pin to  $V_{IN2}$  and  $R_2$  is the resistor from the EN pin to the AGND pin.

$$(EQ. 4) \quad V_{ENABLE} = V_R \cdot \left[ 1 + \frac{R_1}{R_2} \right] + I_{EN} \cdot R_1$$

Once the voltage at the EN pin reaches the enable threshold, the  $I_{EN}$  current sink turns off.

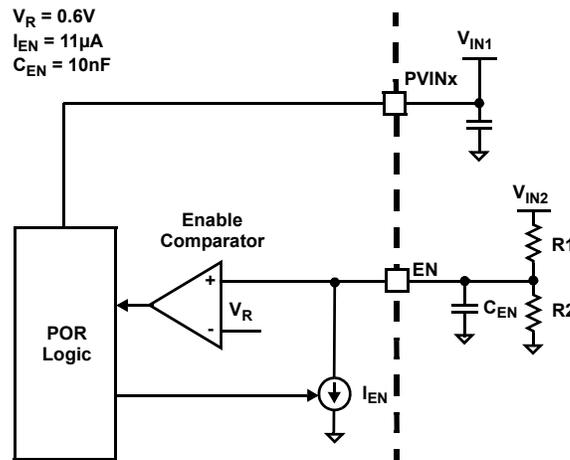


Figure 25. Enable Circuit

With the part enabled and the  $I_{EN}$  current sink off, the disable level is set by the resistor divider. The disable level is defined by [Equation 5](#).

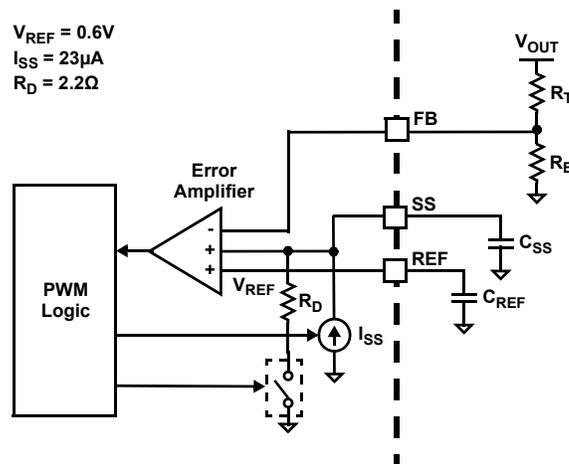
$$(EQ. 5) \quad V_{DISABLE} = V_R \cdot \left[ 1 + \frac{R_1}{R_2} \right]$$

The difference between the enable and disable levels provides adjustable hysteresis so that noise on  $V_{IN2}$  does not interfere with the enabling or disabling of the regulator.

To mitigate single-event transients, the EN pin should be bypassed to the AGND pin with a 10nF ceramic capacitor.

#### 4.2.3 Soft-Start

Once the POR and enable circuits are satisfied, the regulator initiates a soft-start. [Figure 26](#) shows that the soft-start circuit clamps the error amplifier reference voltage to the voltage on an external soft-start capacitor connected to the SS pin.



**Figure 26. Soft-Start Circuit**

The soft-start capacitor is charged by an internal  $I_{SS}$  current source. As the soft-start capacitor is charged, the output voltage slowly ramps to the set point determined by the reference voltage and the feedback network. Once the voltage on the SS pin is equal to the internal reference voltage, the soft-start interval is complete. The controlled ramp of the output voltage reduces the inrush current during start-up. The soft-start output ramp interval is defined in [Equation 6](#) and is adjustable from approximately 2ms to 200ms. The value of the soft-start capacitor,  $C_{SS}$ , should range inclusively from 8.2nF to 8.2μF. The peak inrush current can be computed from [Equation 7](#). The soft-start interval should be long enough to ensure that the peak inrush current plus the peak output load current does not exceed the overcurrent trip level of the regulator.

$$(EQ. 6) \quad t_{SS} = C_{SS} \cdot \frac{V_{REF}}{I_{SS}}$$

$$(EQ. 7) \quad I_{INRUSH} = C_{OUT} \cdot \frac{V_{OUT}}{t_{SS}}$$

The soft-start capacitor is immediately discharged by a 2.2Ω resistor whenever POR conditions are not met or EN is pulled low. The soft-start discharge time is equal to 256 clock cycles.

#### 4.2.4 Power-Good

The Power-Good (PGOOD) pin is an open-drain logic output that indicates when the output voltage of the regulator is within regulation limits. The power-good pin pulls low during shutdown and remains low when the controller is enabled. After a successful soft-start, the PGOOD pin releases, and the voltage rises with an external pull-up resistor. The power-good signal transitions low immediately when the EN pin is pulled low.

The power-good circuitry monitors the FB pin and compares it to the rising and falling thresholds shown in the “Electrical Specifications” table on [page 10](#). If the feedback voltage exceeds the typical rising limit of 111% of the reference voltage, the PGOOD pin pulls low. The PGOOD pin continues to pull low until the feedback voltage falls to a typical of 107.5% of the reference voltage. If the feedback voltage drops below a typical of 89% of the reference voltage, the PGOOD pin pulls low. The PGOOD pin continues to pull low until the feedback voltage rises to a typical 92.5% of the reference voltage. The PGOOD pin then releases and signals the return of the output voltage to within the power-good window.

The PGOOD pin can be pulled up to any voltage from 0V to 5.5V, independently from the supply voltage. The pull-up resistor should have a nominal value from 1kΩ to 10kΩ. The PGOOD pin should be bypassed to DGND, with a 10nF ceramic capacitor to mitigate single-event transients.

### 4.3 Fault Monitoring and Protection

The ISL71001M actively monitors output voltage and current to detect fault conditions. Fault conditions trigger protective measures to prevent damage to the regulator and external load device.

#### 4.3.1 Undervoltage Protection

A hysteretic comparator monitors the FB pin of the regulator. The feedback voltage is compared to an undervoltage threshold that is a fixed percentage of the reference voltage. Once the comparator trips, indicating a valid undervoltage condition, an undervoltage counter increments. The counter is reset if the feedback voltage rises back above the undervoltage threshold, plus a specified amount of hysteresis outlined in the “Electrical Specifications” table on page [page 10](#). If the undervoltage condition exists for three consecutive counts, the counter overflows and the undervoltage protection logic shuts down the regulator.

After the regulator shuts down, it enters a delay interval equivalent to the soft-start interval, which allows the device to cool. The undervoltage counter is reset when the device enters the delay interval. The protection logic initiates a normal soft-start once the delay interval ends. If the output successfully soft-starts, the power-good signal goes high, and normal operation continues. If undervoltage conditions continue to exist during the soft-start interval, the undervoltage counter must overflow before the regulator shuts down again. This hiccup mode continues indefinitely until the output soft-starts successfully.

#### 4.3.2 Overcurrent Protection

A pilot device integrated into the PMOS transistor of Power Block 4 samples current each cycle. This current feedback is scaled and compared to an overcurrent threshold based on the number of power blocks connected. Each additional power block connected beyond Power Block 4 increases the overcurrent limit by 2A. For example, if three power blocks are connected, the typical current limit threshold would be  $3 \times 2A = 6A$ .

If the sampled current exceeds the overcurrent threshold, an overcurrent counter increments by one. Once the overcurrent counter reaches a count of 3, it overflows and the regulator shuts down. If the sampled current falls below the threshold before the counter overflows, the counter is reset.

After the regulator shuts down, it enters a delay interval, equivalent to the soft-start interval, which allows the device to cool. The overcurrent counter is reset when the device enters the delay interval. The protection logic initiates a normal soft-start once the delay interval ends. If the output successfully soft-starts, the power-good signal goes high, and normal operation continues. If overcurrent conditions continue to exist during the soft-start interval, the overcurrent counter must overflow before the regulator shuts down the output again. This hiccup mode continues indefinitely until the output soft-starts successfully.

Note, to prevent severe negative ringing that can disturb the overcurrent counter, it is recommended that a Schottky diode of appropriate rating be added from the LXx pins to the PGNDx pins.

### 4.4 Feedback Loop Compensation

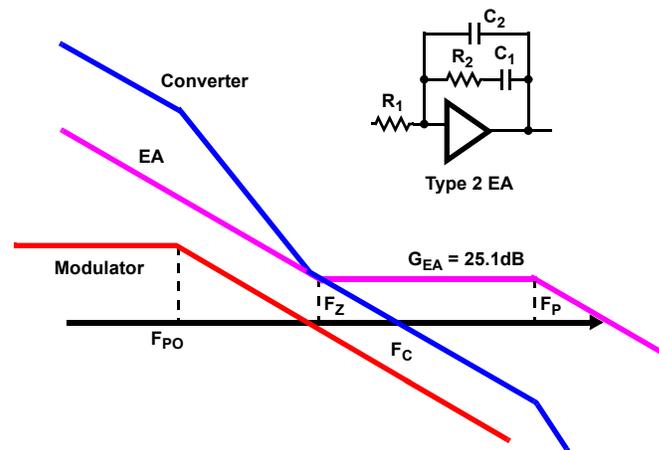
To reduce the number of external components and to simplify the process of determining compensation components, the ISL71001M buck regulator has an internally compensated error amplifier.

Due to the current loop feedback in peak current mode control, the modulator has a single-pole response with -20dB slope at a frequency determined by the load ([Equation 8](#)):

$$(EQ. 8) \quad F_{PO} = \frac{1}{2\pi \cdot R_O \cdot C_{OUT}}$$

where  $R_O$  is load resistance and  $C_{OUT}$  is the output load capacitance. For this type of modulator, a Type 2 compensation circuit is usually sufficient.

[Figure 27 on page 19](#) shows a Type 2 amplifier and its response, along with the responses of the current-mode modulator and the converter.



**Figure 27. Feedback Loop Compensation**

The Type 2 amplifier, in addition to the pole at origin, has a zero-pole pair that causes a flat gain region at frequencies between the zero and the pole ([Equations 9](#) and [10](#)).

$$(EQ. 9) \quad F_Z = \frac{1}{2\pi \cdot R_2 \cdot C_1} = 8.6\text{kHz}$$

$$(EQ. 10) \quad F_P = \frac{1}{2\pi \cdot R_1 \cdot C_2} = 546\text{kHz}$$

Zero frequency and amplifier high-frequency gain were chosen to satisfy typical applications. The crossover frequency will appear at the point where the modulator attenuation equals the amplifier high frequency gain. The only task that the system designer has to complete is to specify the output filter capacitors, to position the load main pole somewhere within one decade lower than the amplifier zero frequency. [Equation 13 on page 20](#) approximates the amount of capacitance needed to achieve an optimal pole location depending on the number of LXx pins connected. With this type of compensation, plenty of phase margin is easily achieved due to zero-pole pair phase ‘boost’.

Conditional stability may occur only when the main load pole is positioned too much to the left side on the frequency axis due to excessive output filter capacitance. In this case, the ESR zero placed within the 1.2kHz to 30kHz range gives some additional phase ‘boost’. Some phase boost is also achieved by connecting the recommended capacitor  $C_C$  in parallel with the upper resistor  $R_T$  of the divider that sets the output voltage value, as demonstrated in [Figure 24 on page 15](#).

## 4.5 Component Selection Guide

This design guide is intended to provide a high-level explanation of the steps necessary to create a power converter. It is assumed the reader is familiar with many of the basic skills and techniques referenced in the following. In addition to this guide, a complete evaluation board that includes schematic, BOM, and an example PCB layout (see the [“Ordering Information” on page 4](#)) is provided.

### 4.5.1 Output Filter Design

The output inductor and the output capacitor bank together form a low-pass filter responsible for smoothing the pulsating voltage at the phase node. The filter must also provide the transient energy until the regulator can respond. Because the filter has low bandwidth relative to the switching frequency, it limits the system transient response. The output capacitors must supply or sink current while the current in the output inductor increases or decreases to meet the load demand.

### 4.5.2 Output Capacitor Selection

The critical load parameters in choosing the output capacitors are the maximum size of the load step ( $\Delta I_{STEP}$ ), the load-current slew rate ( $di/dt$ ), and the maximum allowable output voltage deviation under transient loading ( $\Delta V_{MAX}$ ). Capacitors are characterized according to their capacitance, Equivalent Series Resistance (ESR), and Equivalent Series Inductance (ESL).

At the beginning of a load transient, the output capacitors supply all of the transient current. The output voltage initially deviates by an amount approximated by the voltage drop across the ESL. As the load current increases, the voltage drop across the ESR increases linearly until the load current reaches its final value. Neglecting the contribution of inductor current and regulator response, the output voltage initially deviates by an amount shown in [Equation 11](#).

$$(EQ. 11) \quad \Delta V_{MAX} \approx \left[ ESL \times \frac{di}{dt} \right] + [ESR \times \Delta I_{STEP}]$$

The filter capacitors selected must have sufficiently low ESL and ESR such that the total output voltage deviation is less than the maximum allowable ripple.

Most capacitor solutions rely on a mixture of high frequency capacitors with relatively low capacitance in combination with bulk capacitors having high capacitance but larger ESR. Minimizing the ESL of the high-frequency capacitors allows them to support the output voltage as the current increases. Minimizing the ESR of the bulk capacitors allows them to supply the increased current with less output voltage deviation.

Ceramic capacitors with X7R dielectric are recommended. Alternately, a combination of low ESR solid tantalum capacitors and ceramic capacitors with X7R dielectric may be used.

The ESR of the bulk capacitors is responsible for most of the output voltage ripple. As the bulk capacitors sink and source the inductor AC ripple current, a voltage,  $V_{P-P(MAX)}$ , develops across the bulk capacitor according to [Equation 12](#).

$$(EQ. 12) \quad V_{P-P(MAX)} = ESR \times \left[ \frac{(V_{IN} - V_{OUT})V_{OUT}}{L_{OUT} \times f_s \times V_{IN}} \right]$$

In addition to ESL and ESR, another consideration in selecting the output capacitors is loop stability. The total output capacitance sets the dominant pole of the PWM. Because the ISL71001M uses integrated compensation techniques, it is necessary to restrict the output capacitance to optimize loop stability. The recommended load capacitance can be estimated using [Equation 13](#).

$$(EQ. 13) \quad C_{OUT} = 75\mu F \times \text{Number of LXx Pins Connected} \times \frac{1.8V}{V_{OUT}}$$

Another stability requirement on the selection of the output capacitor is that the ‘ESR zero’ ( $f_{ZESR}$ ) be placed at 60kHz to 90kHz. This range is set by an internal, single compensation zero at 8.6kHz. This ESR zero location contributes to an increased phase margin of the control loop; therefore, if a capacitor is chosen with an inadequate ESR, stability may be compromised. [Equation 14](#) may be used to calculate the required ESR to place the ‘ESR zero’ in the recommended range:

$$(EQ. 14) \quad ESR = \frac{1}{2\pi(f_{ZESR})(C_{OUT})}$$

In conclusion, the output capacitors must meet three criteria:

- (1) They must have sufficient bulk capacitance to sustain the output voltage during a load transient while the output inductor current is slewing to the value of the load transient.
- (2) The ESR must be sufficiently low to meet the desired output voltage ripple due to the output inductor current.
- (3) The ESR zero should be placed, in a rather large range, to provide additional phase margin.

### 4.5.3 Output Inductor Selection

Once the output capacitors are selected, the maximum allowable ripple voltage ( $V_{P-P(MAX)}$ ) determines the lower limit on the inductance as shown in [Equation 15](#).

$$(EQ. 15) \quad L_{OUT} \geq ESR \times \left[ \frac{(V_{IN} - V_{OUT})V_{OUT}}{f_s \times V_{IN} \times V_{P-P(MAX)}} \right]$$

Because the output capacitors are supplying a decreasing portion of the load current while the regulator recovers from the transient, the capacitor voltage becomes slightly depleted. The output inductor must be capable of assuming the entire load current before the output voltage decreases more than  $\Delta V_{MAX}$ . This places an upper limit on inductance.

[Equation 16](#) gives the upper limit on output inductance for the case when the trailing edge of the current transient causes a greater output voltage deviation than the leading edge. [Equation 17](#) addresses the leading edge. Normally, the trailing edge dictates the inductance selection because duty cycles are usually <50%. Nevertheless, both inequalities should be evaluated, and inductance should be governed based on the lower of the two results. In each equation,  $L_{OUT}$  is the output inductance,  $C_{OUT}$  is the total output capacitance, and  $\Delta I_{L(P-P)}$  is the peak-to-peak ripple current in the output inductor.

$$(EQ. 16) \quad L_{OUT} \leq \frac{2 \cdot C_{OUT} \cdot V_{OUT}}{(\Delta I_{STEP})^2} \left[ \Delta V_{MAX} - (\Delta I_{L(P-P)} \cdot ESR) \right]$$

$$(EQ. 17) \quad L_{OUT} \leq \frac{2 \cdot C_{OUT}}{(\Delta I_{STEP})^2} \left[ \Delta V_{MAX} - (\Delta I_{L(P-P)} \cdot ESR) \right] (V_{IN} - V_{OUT})$$

Another concern when selecting an output inductor is to ensure there is adequate slope compensation when the regulator is operated above 50% duty cycle. Because the internal slope compensation is fixed, output inductance should satisfy [Equation 18](#) to ensure this requirement is met.

$$(EQ. 18) \quad L_{OUT} \geq \frac{4.32\mu H}{\text{Number of LXx Pins Connected}}$$

### 4.5.4 Input Capacitor Selection

Input capacitors are responsible for sourcing the AC component of the input current flowing into the switching power devices. Their RMS current capacity must be sufficient to handle the AC component of the current drawn by the switching power devices, which is related to duty cycle. The maximum RMS current required by the regulator is closely approximated by [Equation 19](#).

$$(EQ. 19) \quad I_{RMS_{MAX}} = \sqrt{\frac{V_{OUT}}{V_{IN}} \times \left( I_{OUT(MAX)}^2 + \frac{1}{12} \times \left( \frac{V_{IN} - V_{OUT}}{L_{OUT} \times f_s} \times \frac{V_{OUT}}{V_{IN}} \right)^2 \right)}$$

The important parameters to consider when selecting an input capacitor are the voltage rating and the RMS ripple current rating. For reliable operation, select capacitors with voltage ratings at least 1.5x greater than the maximum input voltage. The capacitor RMS ripple current rating should be higher than the largest RMS ripple current required by the circuit.

Ceramic capacitors with X7R dielectric are recommended. Alternately, a combination of low ESR solid tantalum capacitors and ceramic capacitors with X7R dielectric may be used. The ISL71001M requires a minimum effective input capacitance of 100 $\mu$ F for stable operation.

## 5. PCB Design

PCB design is critical to high-frequency switching regulator performance. Careful component placement and trace routing are necessary to reduce voltage spikes and minimize undesirable voltage drops. Selection of a suitable thermal interface material is also required for optimum heat dissipation and to provide lead strain relief.

### 5.1 PCB Plane Allocation

Four layers of 2 oz. copper are recommended. Layer 2 should be a dedicated ground plane with all critical component ground connections made with vias to this layer. Layer 3 should be a dedicated power plane split between the input and output power rails. Layers 1 and 4 should be used primarily for signals but can also provide additional power and ground islands, as required.

### 5.2 PCB Component Placement

Components should be placed as close as possible to the IC to minimize stray inductance and resistance. Prioritize the placement of bypass capacitors on the pins of the IC in the order shown: REF, SS, AVDD, DVDD, PVINx (high frequency capacitors), EN, PGOOD, PVINx (bulk capacitors).

Locate the output voltage resistive divider as close as possible to the FB pin of the IC. The top leg of the divider should connect directly to the POL (Point of Load), and the bottom leg of the divider should connect directly to AGND. The junction of the resistive divider should connect directly to the FB pin.

A small series R-C snubber connected from the LXx pins to the PGNDx pins may be used to damp high frequency ringing on the LXx pins, if desired, see [Figure 28](#).

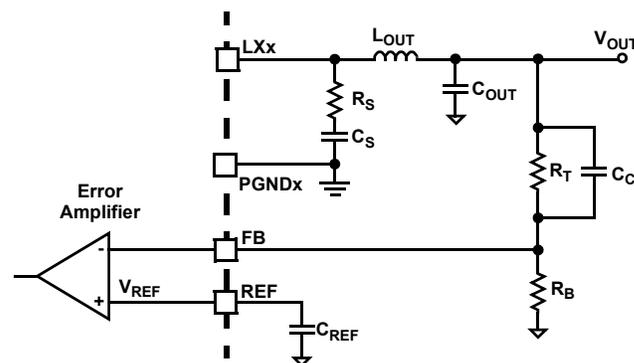


Figure 28. R-C Snubber

### 5.3 PCB Layout

Use a small island of copper to connect the LXx pins of the IC to the output inductor on Layers 1 and 4. To minimize capacitive coupling to the power and ground planes, void the copper on Layers 2 and 3 adjacent to the island.

Keep all other signal traces as short as possible.

### 5.4 Package Thermal Management

For optimum thermal performance, place a pattern of vias and a thermal land on the top layer of the PCB directly underneath the epad. Connect the vias to the plane which serves as a heatsink. To ensure good thermal contact use solder to connect the epad to the thermal land on the PCB. The ISL71001M weighs 0.29 grams.

## 6. Radiation Tolerance

The ISL71001M is a radiation tolerant device for commercial space applications, Low Earth Orbit (LEO) applications, high altitude avionics, launch vehicles, and other harsh environments. This device's response to Total Ionizing Dose (TID) radiation effects and Single-Event Effects (SEE) has been measured, characterized, and reported in the following sections. However, TID performance is not guaranteed through radiation acceptance testing, nor is the SEE characterized performance guaranteed.

### 6.1 Total Ionizing Dose (TID) Testing

#### 6.1.1 Introduction

This test was conducted to determine the sensitivity of the part to the total dose environment. Down points were 0krad(Si), 10krad(Si), 20krad(Si), and 30krad(Si). The irradiations were followed by a biased anneal for 168 hours at +100°C.

Total dose testing was performed using a Hopewell Designs N40 panoramic  $^{60}\text{Co}$  irradiator. The irradiations were performed at 0.00875rad(Si)/s. A PbAl box was used to shield the test fixture and devices under test against low energy secondary gamma radiation.

The characterization matrix consisted of 23 samples irradiated under bias and 21 samples irradiated with all pins grounded. Five control units were used to ensure repeatable data. The bias configuration is shown in [Figure 29](#).

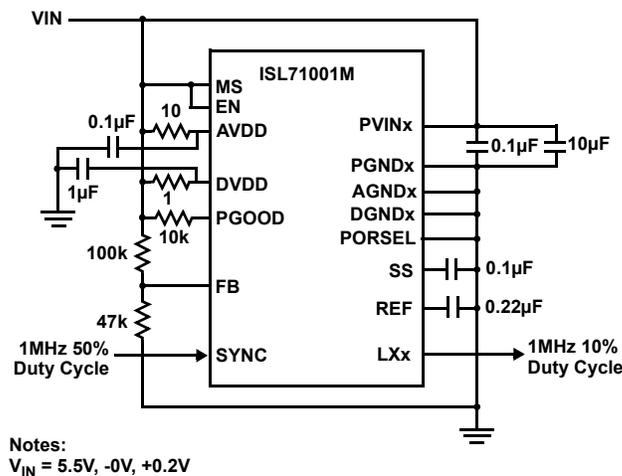


Figure 29. Irradiation Bias Configuration for the IS71001M

All electrical testing was performed outside the irradiator using the production Automated Test Equipment (ATE), with data logging at each down point (including anneal). Down-point electrical testing was performed at room temperature.

### 6.1.2 Results

Table 1 summarizes the attributes data. Note that “Bin 1” indicates a device that passes all datasheet specification limits.

Table 1. ISL71001M Total Dose Test Attributes Data

Dose Rate (mrad(Si)/s)	Bias	Sample Size	Down Point	Bin 1	Rejects
8.75	Figure 29	23	Pre-rad	23	
			10krad(Si)	23	0
			20krad(Si)	23	0
			30krad(Si)	23	0
			Anneal	23	0
8.75	Grounded	21	Pre-rad	21	
			10krad(Si)	21	0
			20krad(Si)	21	0
			30krad(Si)	21	0
			Anneal	21	0

The plots in Figures 30 through 34 show data for key parameters at all down points. The plots show the average as a function of total dose for each of the irradiation conditions; we chose to use the average because of the relatively large sample sizes. All parts showed excellent stability over irradiation.

Table 2 on page 25 shows the average of other key parameters with respect to total dose in tabular form.

### 6.2 Data Plots

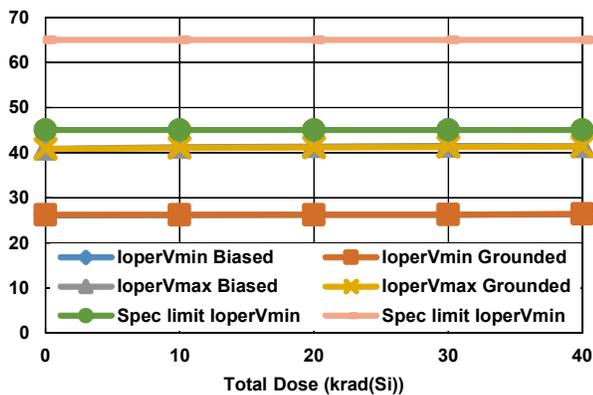


Figure 30. Operating Supply Current vs TID

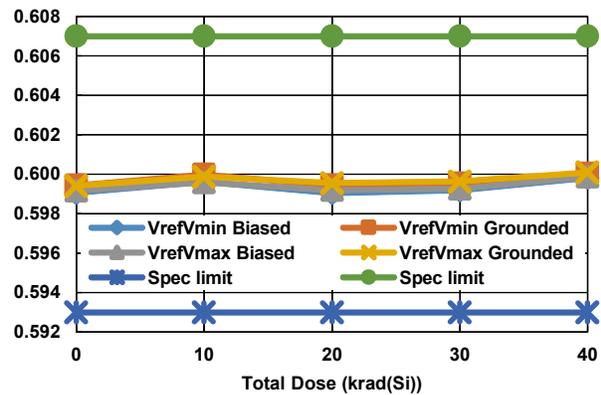


Figure 31. 600mV Reference Voltage vs TID

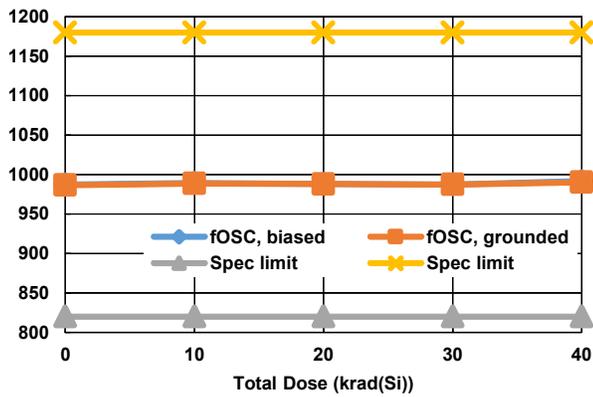


Figure 32. Oscillator Frequency vs TID

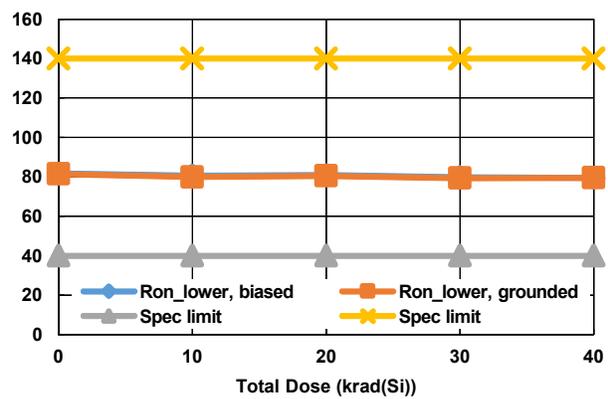


Figure 33. Lower  $r_{DS(ON)}$  vs TID

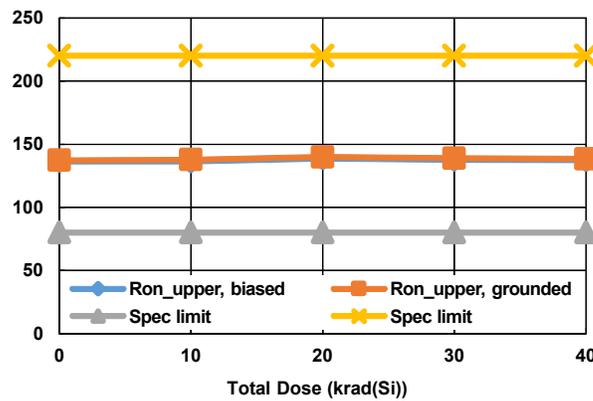


Figure 34. Upper  $r_{DS(ON)}$  vs TID

### 6.2.1 Conclusion

ATE characterization testing showed no rejects to the datasheet limits at all down points. Variables data for selected parameters is presented in [Figures 30](#) through [34](#). No differences between biased and unbiased irradiation were noted, and the part is not considered bias sensitive.

Table 2. ISL71001M Response of Key Parameters vs TID

Parameter	Condition	Bias	0krad(Si)	10krad(Si)	20krad(Si)	30krad(Si)	Anneal	Unit
Operating Supply Current	3.6V Supply	Biased	26.14	26.20	26.23	26.27	26.36	mA
		Grounded	26.24	26.24	26.25	26.26	26.44	mA
	5.5V Supply	Biased	40.84	41.22	41.38	41.49	41.39	mA
		Grounded	40.80	41.03	41.12	41.24	41.34	mA
Shutdown Supply Current	3.6V Supply	Biased	1.37	1.33	1.34	1.45	1.46	mA
		Grounded	1.38	1.33	1.33	1.36	1.60	mA
	5.5V Supply	Biased	2.09	2.11	2.13	2.83	3.26	mA
		Grounded	2.14	2.05	2.00	1.84	2.83	mA
Reference Voltage		Biased	0.599161	0.599586	0.599192	0.599269	0.599869	V
		Grounded	0.599413	0.599881	0.599555	0.599641	0.600098	V

Table 2. ISL71001M Response of Key Parameters vs TID (Continued)

Parameter	Condition	Bias	0krad(Si)	10krad(Si)	20krad(Si)	30krad(Si)	Anneal	Unit
Feedback Pin Leakage Current		Biased	0.004532	0.007303	0.007934	-0.016999	0.00102	μA
		Grounded	0.000719	0.009663	0.005201	-0.009572	-0.00114	μA
Oscillator Accuracy		Biased	987.43	989.28	988.11	987.34	991.49	Hz
		Grounded	986.53	988.47	988.02	987.31	990.20	Hz
Minimum LXx ON Time	3.6V Supply	Biased	141.69	142.17	141.90	142.25	142.86	ns
		Grounded	142.79	142.93	142.71	143.04	144.13	ns
	5.5V Supply	Biased	107.78	108.20	107.84	108.04	108.46	ns
		Grounded	108.27	108.43	108.11	108.26	108.98	ns
Minimum LXx OFF Time	3.6V Supply	Biased	64.78	63.49	63.74	63.67	64.17	ns
		Grounded	65.11	64.00	65.01	64.94	65.24	ns
	5.5V Supply	Biased	40.85	40.08	41.24	41.35	40.22	ns
		Grounded	40.03	39.50	40.40	40.01	39.92	ns
SYNC Input HIGH Threshold		Biased	1.685	1.685	1.690	1.688	1.696	V
		Grounded	1.693	1.697	1.696	1.695	1.698	V
SYNC Input LOW Threshold		Biased	1.487	1.489	1.492	1.489	1.493	V
		Grounded	1.491	1.498	1.498	1.497	1.499	V
SYNC Output LOW Voltage		Biased	140	140.8696	140	140	140	mV
		Grounded	140	140	140	140	140	mV
SYNC Output HIGH Voltage $V_{IN} - V_{OH}$ at $I_{OH} = 1mA$		Biased	160	160	160	160	160	mV
		Grounded	160	160	160	160	160	mV
Upper Device $r_{DS(ON)}$ All Power Blocks in Parallel		Biased	136.40	136.31	138.68	137.59	137.36	mΩ
		Grounded	137.24	137.65	139.84	138.89	138.38	mΩ
Lower Device $r_{DS(ON)}$ All Power Blocks in Parallel		Biased	81.75	80.66	80.89	79.87	79.43	mΩ
		Grounded	81.44	79.98	80.48	79.39	79.52	mΩ
LXx Output Leakage, LX LOW		Biased	0.011828	0.014978	0.012766	0.001502	-0.00288	μA
		Grounded	0.014362	0.016221	0.01326	0.002284	-0.0032	μA
LXx Output Leakage, LX HIGH		Biased	0.013567	0.020225	0.014523	0.010903	0.003164	μA
		Grounded	0.015207	0.0212	0.013284	0.011202	0.002167	μA
VIN POR Start Voltage	PORSEL = GND	Biased	2.781291	2.784805	2.780852	2.783926	2.783048	V
		Grounded	2.779702	2.783069	2.779702	2.782107	2.781145	V
	PORSEL = DVDD	Biased	4.290514	4.289855	4.289855	4.289196	4.290514	V
		Grounded	4.290043	4.289322	4.2886	4.2886	4.290765	V
PGOOD Threshold, Rising $V_{FB}$ as a Percent of $V_{REF}$		Biased	111.75	111.62	111.73	111.72	111.60	%
		Grounded	111.70	111.60	111.68	111.68	111.62	%
PGOOD Threshold, Falling $V_{FB}$ as a Percent of $V_{REF}$		Biased	88.52	88.44	88.53	88.50	88.43	%
		Grounded	88.49	88.37	88.43	88.39	88.36	%
PGOOD Hysteresis, Rising $V_{FB}$ as a Percent of $V_{REF}$		Biased	3.79	3.77	3.76	3.76	3.77	%
		Grounded	3.73	3.73	3.71	3.71	3.75	%
PGOOD Hysteresis, Falling $V_{FB}$ as a Percent of $V_{REF}$		Biased	3.76	3.72	3.70	3.72	3.72	%
		Grounded	3.71	3.71	3.67	3.71	3.69	%

Table 2. ISL71001M Response of Key Parameters vs TID (Continued)

Parameter	Condition	Bias	0krad(Si)	10krad(Si)	20krad(Si)	30krad(Si)	Anneal	Unit
PGOOD Leakage		Biased	0.014196	0.025129	0.013847	0.013412	0.008019	μA
		Grounded	0.012484	0.028836	0.009172	0.014584	0.010116	μA
Undervoltage Trip Threshold		Biased	75.35	75.04	75.35	75.31	75.19	%
		Grounded	75.30	74.98	75.30	75.26	75.15	%
Undervoltage Recovery Threshold		Biased	87.75	87.79	87.87	87.78	87.87	%
		Grounded	87.80	87.65	87.79	87.61	87.82	%
Overcurrent Trip Threshold	3.6V Supply	Biased	1.71	1.73	1.75	1.74	1.78	A
		Grounded	1.70	1.74	1.74	1.74	1.77	A
	5.5V Supply	Biased	1.88	1.91	1.92	1.92	1.94	A
		Grounded	1.88	1.92	1.92	1.92	1.94	A

## 6.3 Single-Event Effects Testing

### 6.3.1 Introduction

The intense heavy ion environment encountered in space applications can cause a variety of Single-Event Effects (SEE). SEE can lead to system-level performance issues including disruption, degradation, and destruction. For predictable and reliable space system operation, individual electronic components should be characterized to determine their SEE response. The following is a summary of the SEE testing of the ISL71001M.

### 6.3.2 SEE Test Setup

Testing was performed at the Texas A&M University (TAMU) Cyclotron Institute heavy ion facility. This facility is coupled to a K500 super-conducting cyclotron, which is capable of generating a wide range of test particles with the various energy, flux, and fluence level needed for advanced radiation testing.

A schematic of the ISL71001M SEE test circuit is shown in [Figure 37](#). The test circuit is a synchronous buck DC/DC converter configured to accept an input voltage from 3V to 5.5V and generate a nominal 1.8V output voltage. Output current was adjusted using a constant current electronic load.

Four test circuits were mounted to a test jig, which could be rotated with respect to the ion beam. A 20 foot coaxial cable connected the test jig to a switch box in the control room, which contained all of the monitoring equipment. The switch box allowed any one of the four test circuits to be controlled and monitored remotely.

Digital multimeters were used to monitor input voltage ( $V_{IN}$ ), output voltage ( $V_{OUT}$ ) and input current ( $I_{IN}$ ). Four LeCroy 4-channel digital oscilloscopes were used to monitor, capture, and store key signal waveforms. [Table 3](#) shows the scope configuration used during the testing.  $\Delta PW$  and  $\Delta T$  refer to change in pulse width and change in period, respectively.

Table 3. ISL71001M Scope Channel Set-Up

SCOPE	CH 1	CH 2	CH 3	CH 4	TRIGGER
1	LX	VOUT	SS	PGOOD	LX ( $\Delta PW = \pm 20\%$ )
2	LX	VOUT	SS	PGOOD	LX ( $\Delta T = +10\%$ )
3	LX	VOUT	SS	PGOOD	LX ( $\Delta T = -10\%$ )
4	LX	VOUT	SS	PGOOD	PGOOD ( $< 2.5V$ )

### 6.3.3 SEL, SEB, and SEGR Testing Results

During SEL, SEB, and SEGR testing, the input voltage ( $V_{IN}$ ) was initially set to 5.5V, which is the maximum recommended supply voltage rating for the device, and then increased in 0.1V increments. Output voltage ( $V_{OUT}$ ) was set to 1.8V. Output current ( $I_{OUT}$ ) was set to 7A, which is 1A above the 6A maximum recommended current rating for the device. Case temperature was maintained at +125°C by controlling current flowing into a resistive heat pad bonded to the underside of the DUT. DUTs were irradiated with Ag ions at a 0° incident angle, resulting in an LET of 43MeV•cm<sup>2</sup>/mg.

Operating input current was measured pre-radiation and post-radiation resulting in <1% increase on four devices at the highest passing supply voltage of 5.7V. The criterion for failure was a greater than 5% increase in operating input current ( $I_{IN}$ ) at  $I_{OUT} = 0A$ .

### 6.3.4 Single Event Transient Testing

Single Event Transient (SET) testing was conducted with 5V input and 3V input. In both cases the output voltage was 1.8V and load current of 4A.

The plots in [Figures 35](#) and [36](#) show the typical SET performance of the ISL71001M.

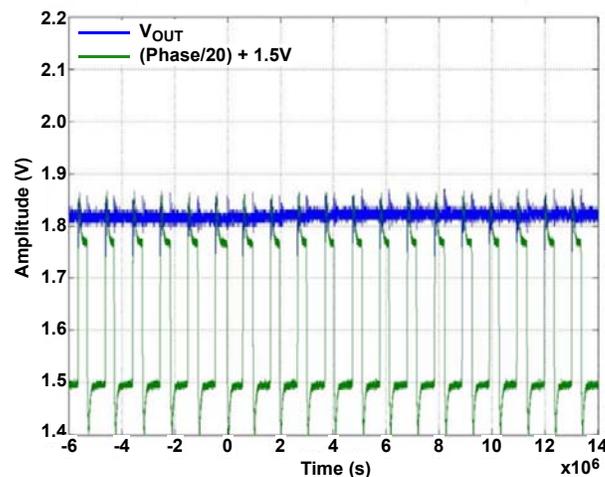


Figure 35. Set Response with 5.5V Input,  $\Delta V_{OUT} < 1\%$

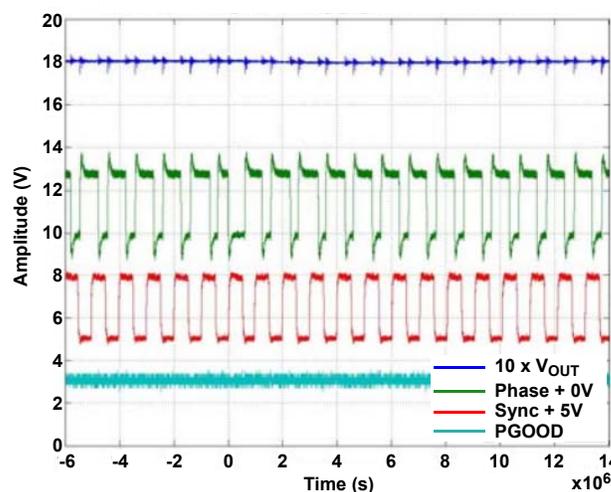


Figure 36. Set Response with 3V Input,  $\Delta V_{OUT} < 1\%$

### 6.3.5 Conclusion

The SEE test results clearly demonstrate that the ISL71001M is robust against SEL, SEB, and SEGR to an LET of  $43\text{MeV}\cdot\text{cm}^2/\text{mg}$  at an input voltage up to 5.7V, an output current up to 7A and a case temperature up to  $+125^\circ\text{C}$ . SET characterization showed the response to be a less than 1% perturbation of the output voltage to an effective LET of  $43\text{MeV}\cdot\text{cm}^2/\text{mg}$ .

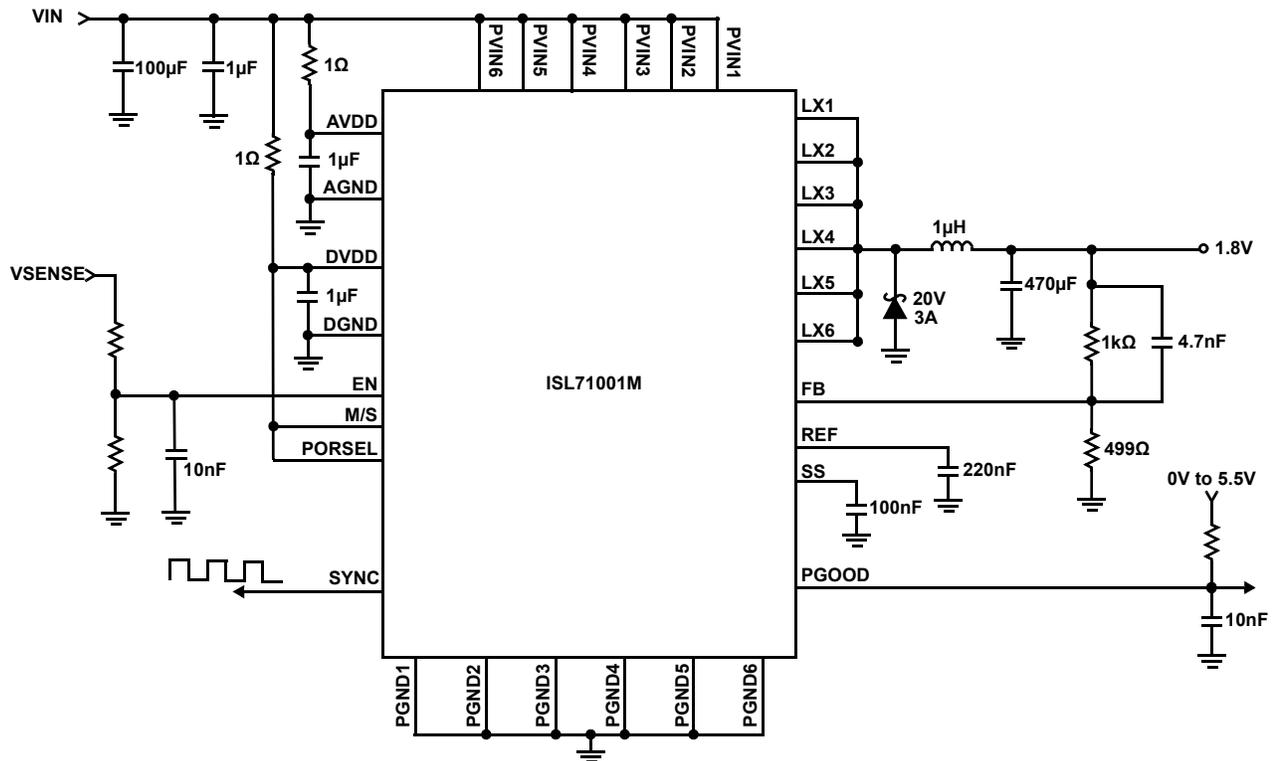


Figure 37. Simplified Schematic of ISL71001M SEE Test Circuit

## 7. Revision History

Rev.	Date	Description
1.00	Mar 26, 2018	Updated to latest layout. Added Outgassing Feature bullet. Updated Ordering information by adding -T part to table and updated Note 1. Added Outgassing specification information. Updated Figure 21. Removed About Intersil section and updated disclaimer.
0.00	Mar 24, 2017	Initial release

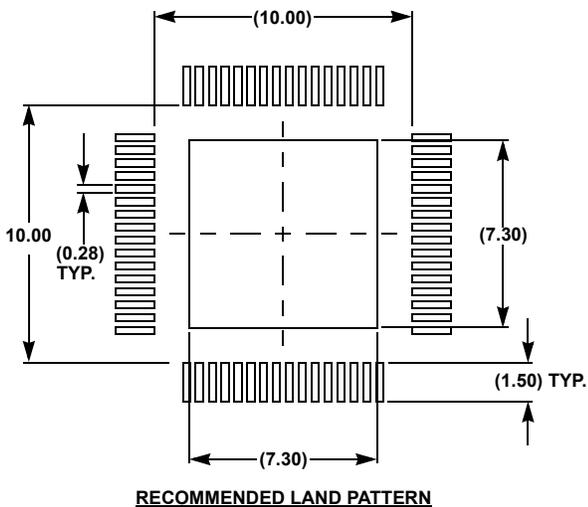
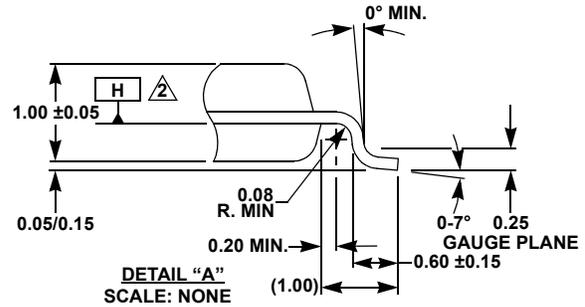
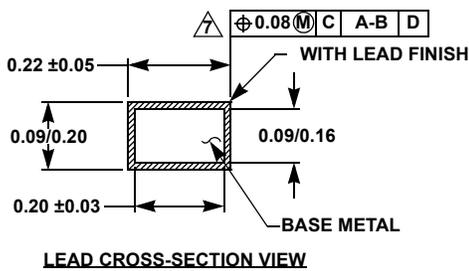
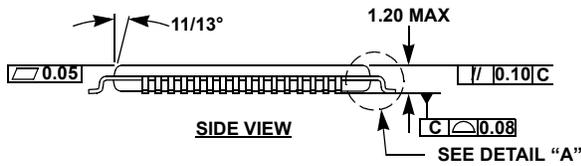
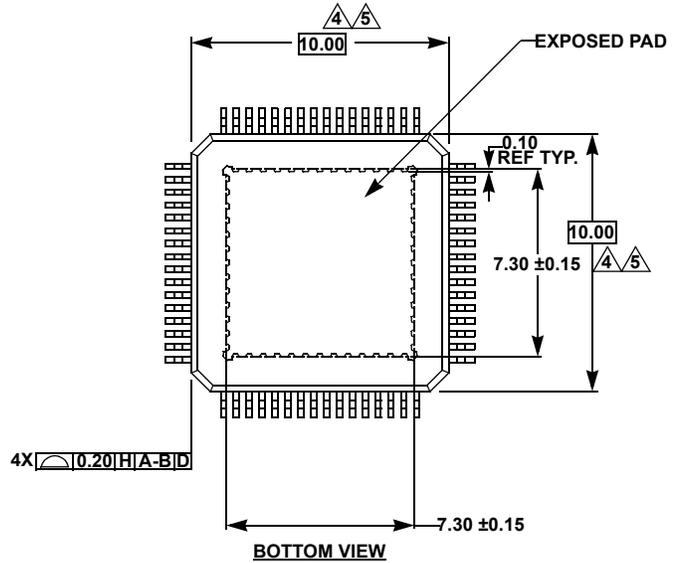
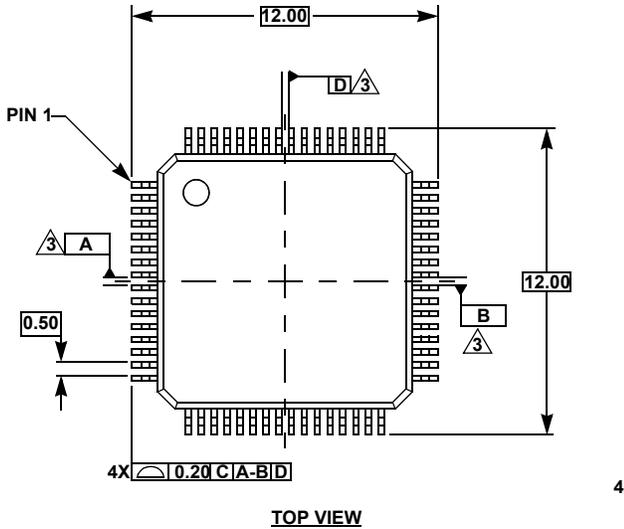
# 8. Package Outline Drawing

For the most recent package outline drawing, see [Q64.10x10J](#).

Q64.10x10J

64 LEAD THIN PLASTIC QUAD FLATPACK PACKAGE WITH EXPOSED PAD (EP-TQFP)

Rev 0, 5/16



**NOTES:**

1. All dimensioning and tolerancing conform to ANSI Y14.5-1982.
2. Datum plane H located at mold parting line and coincident with lead, where lead exits plastic body at bottom of parting line
3. Datums A-B and D to be determined at centerline between leads where leads exit plastic body at datum plane H.
4. Dimensions do not include mold protrusion. Allowable mold protrusion is 0.254mm on these dimensions.
5. These dimensions to be determined at datum plane H.
6. Package top dimensions are smaller than bottom dimensions and top of package will not overhang bottom of package.
7. Lead width dimension does not include dambar protrusion. All dambar protrusion shall be 0.08mm total in excess of the dime maximum material condition. Dambar cannot be located on the radius or the foot.
8. Controlling dimension: millimeter.
9. This outline conforms to JEDEC publication 95 registration MS-026, variation ACD.
10. Dimensions in ( ) are for reference only.

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